



## NL9620

### Precision Low Power Instrumentation Amplifier

#### FEATURES

Gain Set with One External Resistor	
Gain Range	1 to 10,000
Low Input Offset Voltage	
$T_a = 25^\circ\text{C}$	125 $\mu\text{V}$ max.
$T_a = -40$ to $85^\circ\text{C}$	185 $\mu\text{V}$ max.
Input Offset Voltage Drift	1 $\mu\text{V}/^\circ\text{C}$ max.
Input Bias Current	2 nA max.
Supply Current	0.9mA typ. 1.3mA max.
Common-Mode Rejection Ratio (@ $G = 100$ )	110dB min.
Supply Voltage	$\pm 2.3\text{V}$ to $\pm 18\text{V}$
Integrated EMI filter	
Voltage Noise ( $f = 1\text{kHz}$ )	13nV/ $\sqrt{\text{Hz}}$ max.
-3dB Bandwidth ( $G = 100$ )	120kHz typ.
Slew Rate	0.75V/ $\mu\text{s}$ min.
Bipolar Architecture	
Operating Temperature (Specified)	-40°C to 85°C
Package	VSP-8-AF, EMP-8-AN

#### APPLICATIONS

Battery-powered Equipment
Sensor Interface
Strain Gauge, Flow Meter, Pressure Sensor
Transducer Interface

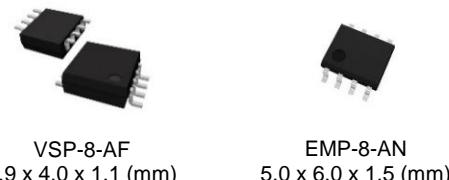
#### GENERAL DESCRIPTION

The NL9620 is a high precision, low power instrumentation amplifier that requires only one external resistor to set gains of 1 to 10,000, and using bipolar process.

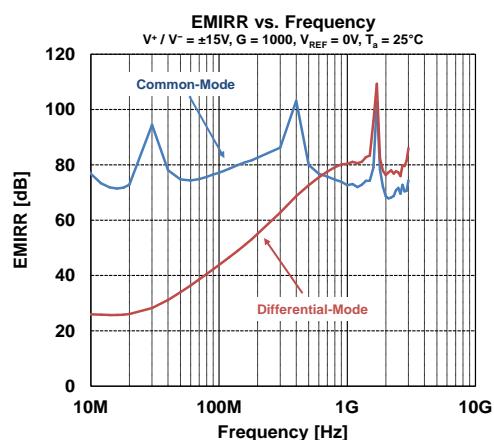
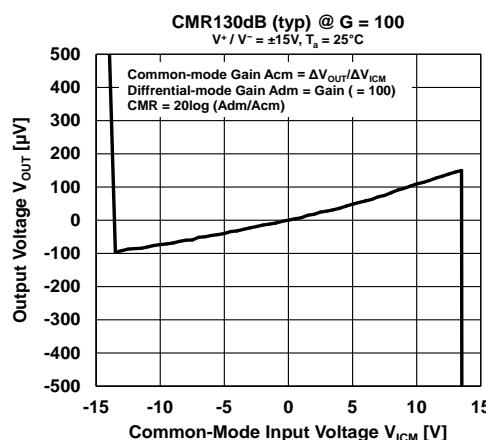
Characteristics such as low input offset voltage (125  $\mu\text{V}$  max.), Low input offset voltage drift (1  $\mu\text{V}/^\circ\text{C}$  max.), High CMR (110 dB min. at  $G = 100$ ), and low input bias current (2 nA max.) It is ideal for systems that required to sense signals from various sensors with high accuracy, such as transducer interfaces and weigh scales. It also has low supply current (1.3mA max.), which makes it ideal for battery-powered equipment applications.

Since it has a built-in integrated EMI filter, it reduces malfunctions due to the influence of high frequencies such as mobile phones.

NL9620 is available in 8-pin VSP and EMP packages.



VSP-8-AF  
2.9 x 4.0 x 1.1 (mm)  
EMP-8-AN  
5.0 x 6.0 x 1.5 (mm)



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## ■ PRODUCT NAME INFORMATION

NL9620 aa A bb D

Description of configuration

Composition	Item	Description
aa	Package code	Indicates the package. AF: VSP-8-AF AN: EMP-8-AN
A	Version	Product version. A: Default
bb	Packing	E2: Insert Direction. Refer to the packing specifications.
D	Grade	Indicates the quality grade. D: Industrial

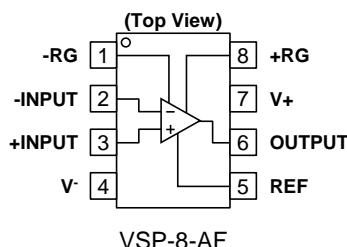
Grade

	Applications	Operating Temperature Range	Test Temperature
D	Industrial equipment and Social infrastructures	-40°C to 125°C	-40, 25°C, 85°C

## ■ ORDER INFORMATION

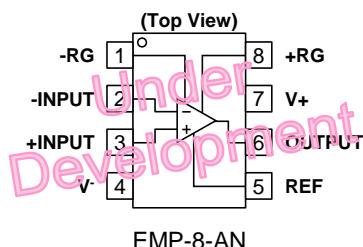
Product Name	Package	RoHS	Halogen-Free	Plating Composition	Weight (mg)	Quantity (pcs/reel)
NL9620AFAE2D	VSP-8-AF	✓	✓	Sn2Bi	21	2000
NL9620ANAE2D	EMP-8-AN	✓	✓	Sn2Bi	76	2000

## ■ PIN DESCRIPTIONS (NL9620AF)



Pin No.	Pin Name	I/O	Description
1	-RG	-	Gain setting pin. Place a gain resistor between pin 1 and pin 8.
2	-INPUT	I	Inverting input
3	+INPUT	I	Non-inverting input
4	V-	-	Negative supply
5	REF	I	Reference input. This pin must be driven by low impedance.
6	OUTPUT	O	Output
7	V+	-	Positive supply
8	+RG	-	Gain setting pin. Place a gain resistor between pin 1 and pin 8.

## ■ PIN DESCRIPTIONS (NL9620AN)



Pin No.	Pin Name	I/O	Description
1	-RG	-	Gain setting pin. Place a gain resistor between pin 1 and pin 8.
2	-INPUT	I	Inverting input
3	+INPUT	I	Non-inverting input
4	V <sup>-</sup>	-	Negative supply
5	REF	I	Reference input. This pin must be driven by low impedance.
6	OUTPUT	O	Output
7	V <sup>+</sup>	-	Positive supply
8	+RG	-	Gain setting pin. Place a gain resistor between pin 1 and pin 8.

## ■ ABSOLUTE MAXIMUM RATINGS

	Symbol	Ratings	Unit
Supply Voltage	V <sup>+</sup> / V <sup>-</sup>	±18	V
Input Voltage (+INPUT, -INPUT, REF ) <sup>*1</sup>	V <sub>IN</sub>	±18	V
Input Current <sup>*2</sup>	I <sub>IN</sub>	±10	mA
Differential Input Voltage <sup>*3</sup>	V <sub>ID</sub>	Gain ≤ 50 ; ±50/Gain <sup>*1</sup> Gain > 50 ; ±1	V
Output Short-Circuit Duration <sup>*4</sup>		Continuous	
Storage Temperature	T <sub>stg</sub>	-55 to 150	°C
Junction Temperature <sup>*5</sup>	T <sub>j</sub>	150	°C

<sup>\*1</sup> For supply voltage less than ±18V, the absolute maximum rating is equal to the supply voltage.

<sup>\*2</sup> Input voltages outside the supply voltage will be clamped by ESD protection diodes. If the input voltage exceeds the supply voltage, the current must be limited 10 mA or less by using a restriction resistance. Input current inflow is positive and Input current outflow is negative.

<sup>\*3</sup> Differential voltage is the voltage difference between +INPUT and -INPUT.

<sup>\*4</sup> Power loss increases when output is short-circuited; do not exceed T<sub>j</sub>.

<sup>\*5</sup> Calculate the power consumption of the IC from the operating conditions, and calculate the junction temperature with the thermal resistance.

Please refer to "Thermal characteristics" for the thermal resistance under our measurement board conditions.

## ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the lifetime and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings is not assured.

## ■ THERMAL CHARACTERISTICS

Package	Measurement Result <sup>*1</sup>		Unit
	θ <sub>ja</sub>	ψ <sub>jt</sub>	
VSP-8-AF	152	24	
EMP-8-AN	104	12	°C/W

θ<sub>ja</sub>: Junction-to-Ambient Thermal Resistance

ψ<sub>jt</sub>: Junction-to-Top Thermal Characterization Parameter

<sup>\*1</sup> Mounted on glass epoxy board (76.2 mm × 114.3 mm × 1.6 mm: based on EIA/JEDEC standard, 4-layer FR-4), internal Cu area: 74.2 mm × 74.2 mm.

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## ■ ELECTROSTATIC DISCHARGE (ESD) PROTECTION VOLTAGE

	Conditions	Protection Voltage
HBM	$C = 100 \text{ pF}$ , $R = 1.5 \text{ k}\Omega$	$\pm 2000\text{V}$
CDM		$\pm 1000\text{V}$

## ELECTROSTATIC DISCHARGE RATINGS

The electrostatic discharge test is done based on JEDEC JS001 and JS002.

In the HBM method, ESD is applied using the power supply pin and GND pin as reference pins.

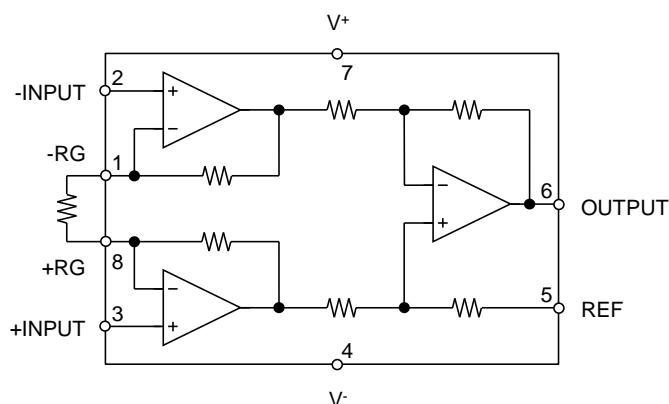
## ■ RECOMMENDED OPERATING CONDITIONS

	Symbol	Ratings	Unit
Supply Voltage	V <sup>+</sup> / V <sup>-</sup>	±2.3 to ±18	V
Operating Temperature Range	T <sub>a</sub>	-40 to 85 (Specified) -40 to 125 (Operating)	°C

## RECOMMENDED OPERATING CONDITIONS

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

## ■ BLOCK DIAGRAM



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## ELECTRICAL CHARACTERISTICS

$V^+ / V^- = \pm 15V$ ,  $V_{REF}=0V$ ,  $R_L = 5k\Omega$ ,  $T_a = 25^\circ C$ , unless otherwise specified.

Parameter	Symbol	Conditions	MIN	TYP	MAX	Unit
<b>Gain <sup>*1</sup></b>						
Gain Range			1	-	10,000	
Gain Error <sup>*2</sup>	$G_{err}$	$V_{OUT} = \pm 10V$				
		$G = 1$	-	0.03	0.10	%
		$G = 10$	-	0.15	0.30	%
		$G = 100$	-	0.15	0.30	%
		$G = 1000$	-	0.40	0.70	%
Nonlinearity	NL	$V_{OUT} = -10$ to $10V$ , $R_L = 10k\Omega$				
		$G = 1-100$	-	10	40	ppm
		$G = 1000$	-	40	-	ppm
		$V_{OUT} = -10$ to $10V$ , $R_L = 5k\Omega$				
Gain vs. Temperature	$\Delta G/\Delta T$	$G = 1-100$	-	10	95	ppm
		$T_a = -40^\circ C$ to $85^\circ C$				
		$G = 1$	-	-	10	ppm/°C
$G > 1$ <sup>*2</sup>			-	-	50	ppm/°C
<b>Offset Voltage <sup>*3</sup></b>						
Input Offset Voltage	$V_{OSI}$	$V^+ / V^- = \pm 5V$ to $\pm 15V$	-	30	125	µV
		$V^+ / V^- = \pm 5V$ to $\pm 15V$ , $T_a = -40^\circ C$ to $85^\circ C$	-	-	185	µV
Input Offset Voltage Drift	$\Delta V_{OSI}/\Delta T$	$V^+ / V^- = \pm 5V$ to $\pm 15V$ , $T_a = -40^\circ C$ to $85^\circ C$ , VSP-8-AF	-	0.3	1.3	µV/°C
		$V^+ / V^- = \pm 5V$ to $\pm 15V$ , $T_a = -40^\circ C$ to $85^\circ C$ , EMP-8-AN	-	0.3	1.0	µV/°C
Output Offset Voltage	$V_{OSO}$	$V^+ / V^- = \pm 15V$	-	400	1000	µV
		$V^+ / V^- = \pm 5V$	-	-	1500	µV
		$V^+ / V^- = \pm 5V$ to $\pm 15V$ , $T_a = -40^\circ C$ to $85^\circ C$	-	-	2000	µV
Output Offset Voltage Drift	$\Delta V_{OSO}/\Delta T$	$V^+ / V^- = \pm 5V$ to $\pm 15V$ , $T_a = -40^\circ C$ to $85^\circ C$	-	5	15	µV/°C
Supply Voltage Rejection Ratio	SVR	$V^+ / V^- = \pm 2.3V$ to $\pm 18V$				
		$G = 1$	80	100	-	dB
		$G = 10$	95	120	-	dB
		$G = 100$	110	140	-	dB
		$G = 1000$	110	140	-	dB
<b>Input Current</b>						
Input Bias Current	$I_B$	$T_a = 25^\circ C$	-	0.5	2.0	nA
		$T_a = -40^\circ C$ to $85^\circ C$	-	-	2.5	nA
Input Bias Current Drift	$\Delta I_B/\Delta T$	$T_a = -40^\circ C$ to $85^\circ C$	-	3.0	-	pA/°C
Input Offset Current	$I_{IO}$	$T_a = 25^\circ C$	-	0.3	1.0	nA
		$T_a = -40^\circ C$ to $85^\circ C$	-	-	1.5	nA
Input Offset Current Drift	$\Delta I_{IO}/\Delta T$	$T_a = -40^\circ C$ to $85^\circ C$	-	1.5	-	pA/°C

<sup>\*1</sup> Gain =  $1 + (49.4k\Omega / R_G)$

<sup>\*2</sup> Does not include effects of external resistor  $R_G$ .

<sup>\*3</sup> Total RTI Error =  $V_{OSI} + V_{OSO}/G$

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## ELECTRICAL CHARACTERISTICS 2

$V^+ / V^- = \pm 15V$ ,  $V_{REF}=0V$ ,  $R_L = 5k\Omega$ ,  $T_a = 25^\circ C$ , unless otherwise specified.

Parameter	Symbol	Conditions	MIN	TYP	MAX	Unit
<b>Input</b>						
Input Resistance	$R_{IN}$	Differential Common-Mode	-	60	-	$\text{G}\Omega$
			-	70	-	$\text{G}\Omega$
Input Capacitance	$C_{IN}$	Differential Common-Mode	-	6	-	$\text{pF}$
			-	2	-	$\text{pF}$
Input Voltage Range <sup>1</sup>	$V_{ICM}$	$V^+ / V^- = \pm 2.3V$ to $\pm 5V$ $V^+ / V^- = \pm 2.3V$ to $\pm 5V$ , $T_a = -40^\circ C$ to $85^\circ C$ $V^+ / V^- = \pm 5V$ to $\pm 18V$ $V^+ / V^- = \pm 5V$ to $\pm 18V$ , $T_a = -40^\circ C$ to $85^\circ C$	$V^- + 1.7$	-	$V^+ - 1.4$	V
			$V^- + 1.7$	-	$V^+ - 1.6$	V
			$V^- + 1.7$	-	$V^+ - 1.4$	V
			$V^- + 1.7$	-	$V^+ - 1.6$	V
Common-Mode Rejection Ratio						
Common-Mode Rejection Ratio	CMR	DC with $1k\Omega$ Source Imbalance, $V_{CM} = 0V$ to $\pm 10V$				
		$G = 1$	73	90	-	$\text{dB}$
		$G = 10$	93	110	-	$\text{dB}$
		$G = 100$	110	130	-	$\text{dB}$
		$G = 1000$	110	130	-	$\text{dB}$
		$f = 60\text{Hz}$ with $1k\Omega$ Source Imbalance, $V_{IN} = 20V_{PP}$				
		$G = 1$	-	90	-	$\text{dB}$
		$G = 10$	-	110	-	$\text{dB}$
		$G = 100$	-	110	-	$\text{dB}$
		$G = 1000$	-	110	-	$\text{dB}$
<b>Output</b>						
High-level Output Voltage	$V_{OH}$	$V^+ / V^- = \pm 2.3V$ to $\pm 5V$ , $R_L = 10k\Omega$ $V^+ / V^- = \pm 2.3V$ to $\pm 5V$ , $R_L = 10k\Omega$ , $T_a = -40^\circ C$ to $85^\circ C$ $V^+ / V^- = \pm 5V$ to $\pm 18V$ , $R_L = 10k\Omega$ $V^+ / V^- = \pm 5V$ to $\pm 18V$ , $R_L = 10k\Omega$ , $T_a = -40^\circ C$ to $85^\circ C$	-	-	$V^+ - 1.2$	V
			-	-	$V^+ - 1.3$	V
			-	-	$V^+ - 1.4$	V
			-	-	$V^+ - 1.5$	V
Low-level Output Voltage	$V_{OL}$	$V^+ / V^- = \pm 2.3V$ to $\pm 5V$ , $R_L = 10k\Omega$ $V^+ / V^- = \pm 2.3V$ to $\pm 5V$ , $R_L = 10k\Omega$ , $T_a = -40^\circ C$ to $85^\circ C$ $V^+ / V^- = \pm 5V$ to $\pm 18V$ , $R_L = 10k\Omega$ $V^+ / V^- = \pm 5V$ to $\pm 18V$ , $R_L = 10k\Omega$ , $T_a = -40^\circ C$ to $85^\circ C$	$V^- + 1.1$	-	-	V
			$V^- + 1.4$	-	-	V
			$V^- + 1.2$	-	-	V
			$V^- + 1.6$	-	-	V
Output Short-Circuit Current	$I_{SC}$	Source Sink	-	18	-	$\text{mA}$
			-	18	-	$\text{mA}$
<b>Reference Input</b>						
Input Resistance	$R_{IN(REF)}$		-	40	-	$\text{k}\Omega$
Input Current	$I_{IN(REF)}$	$G = 1$ , $V_{IN+} = V_{IN-} = V_{REF} = 0$	-	30	50	$\mu\text{A}$
Input Voltage Range	$V_{ICM(REF)}$		$V^- + 1.6$	-	$V^+ - 1.6$	V
Gain	$G_{(REF)}$		-	$1 \pm 0.0001$	-	
<b>Power Supply</b>						
Supply Current	$I_{SUPPLY}$	$V^+ / V^- = \pm 2.3V$ to $\pm 18V$ $V^+ / V^- = \pm 2.3V$ to $\pm 18V$ , $T_a = -40^\circ C$ to $85^\circ C$	-	0.9	1.3	$\text{mA}$
			-	1.1	1.6	$\text{mA}$

<sup>1</sup> One input grounded.  $G = 1$ .

## ■ ELECTRICAL CHARACTERISTICS 3

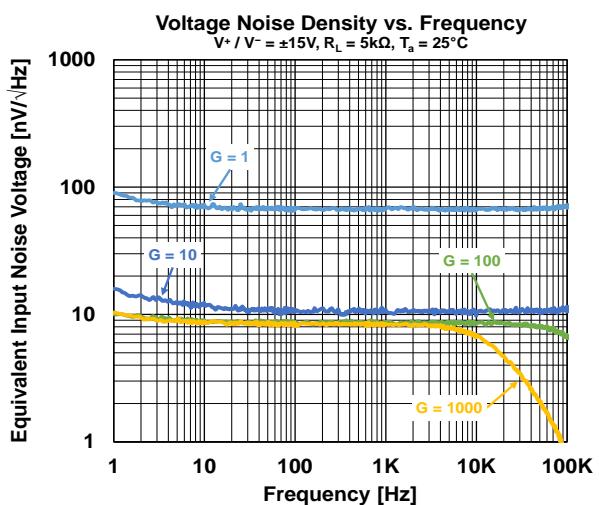
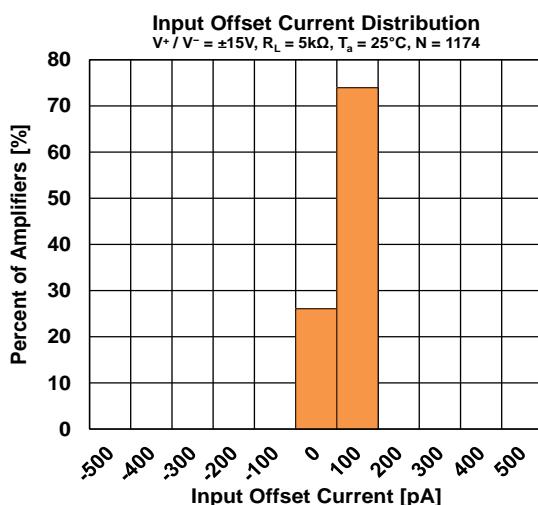
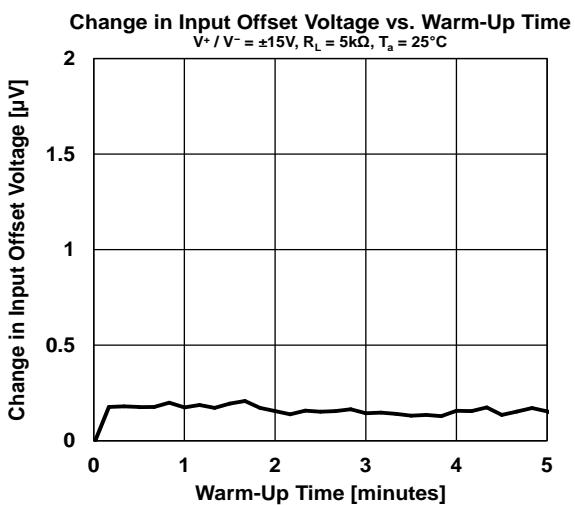
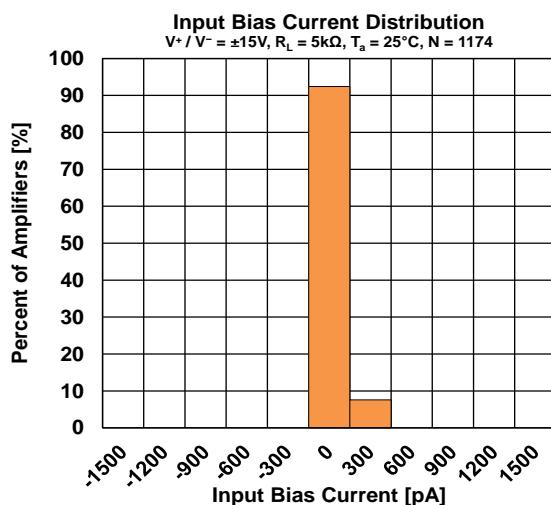
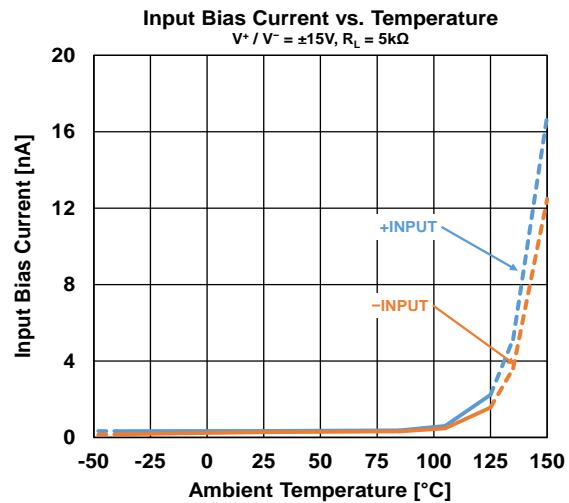
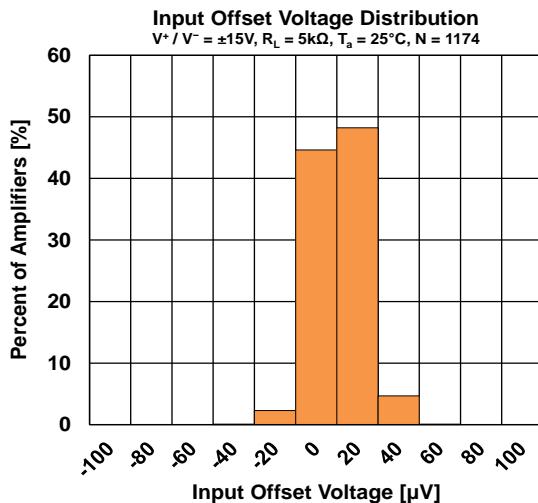
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Parameter	Symbol	Conditions	MIN	TYP	MAX	Unit
<b>Frequency Response</b>						
-3dB Bandwidth	BW <sub>-3dB</sub>	G = 1	-	1000	-	kHz
		G = 10	-	800	-	kHz
		G = 100	-	120	-	kHz
		G = 1000	-	12	-	kHz
Slew Rate	SR	G = 1, $V_{IN+} = 20V_{PP}$ , $V_{IN-} = 0V$	0.75	1.20	-	V/μs
Settling Time	t <sub>s</sub>	0.01%, $V_{OUT} = 10V_{PP}$	-	15	-	μs
		G = 1-100	-	150	-	μs
<b>Noise</b> *1						
Input Noise Voltage	e <sub>ni</sub>	f = 1kHz	-	9	13	nV/√Hz
Output Noise Voltage	e <sub>no</sub>	f = 1kHz	-	72	100	nV/√Hz
Equivalent Input Noise Voltage	V <sub>NI</sub>	f = 0.1Hz to 10Hz	-	3.00	-	μV <sub>PP</sub>
		G = 1	-	0.55	-	μV <sub>PP</sub>
		G = 10	-	0.28	-	μV <sub>PP</sub>
Input Noise Current	i <sub>n</sub>	f = 1kHz	-	285	-	fA/√Hz
	I <sub>n</sub>	f = 0.1Hz to 10Hz	-	10	-	pApp

<sup>\*1</sup> Total RTI Noise =  $\sqrt{(e_{ni})^2 + (e_{no}/G)^2}$

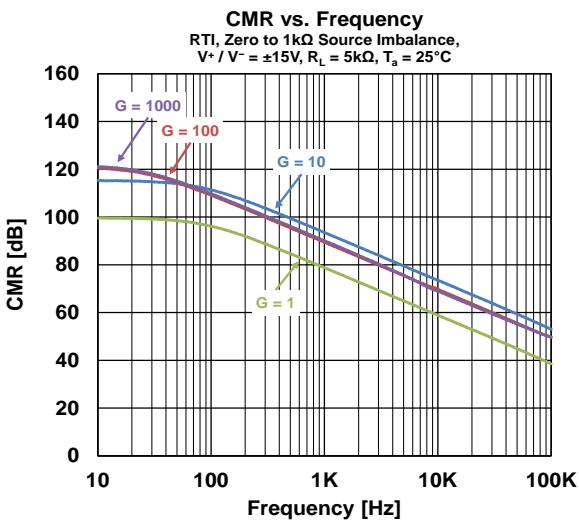
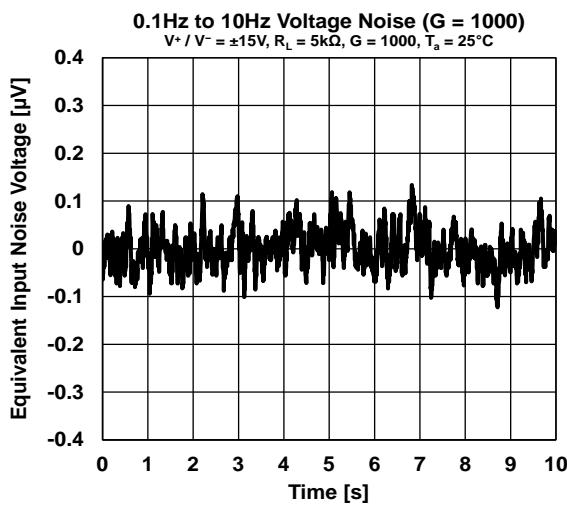
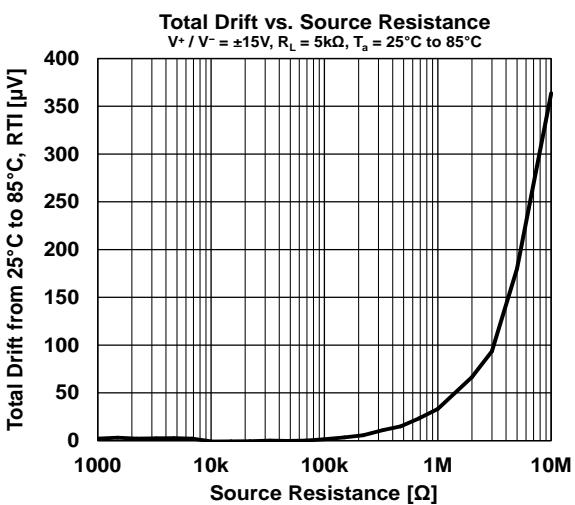
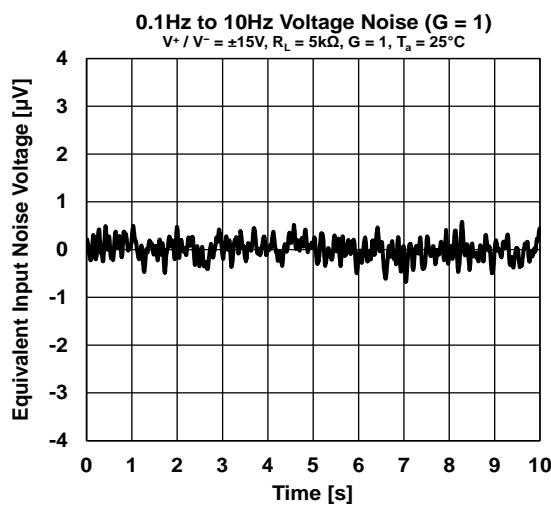
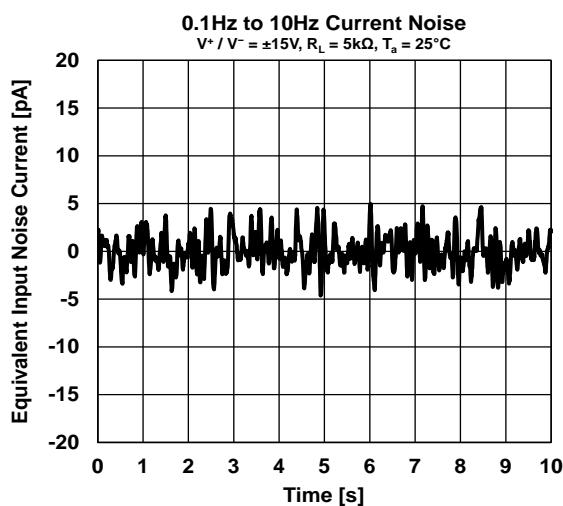
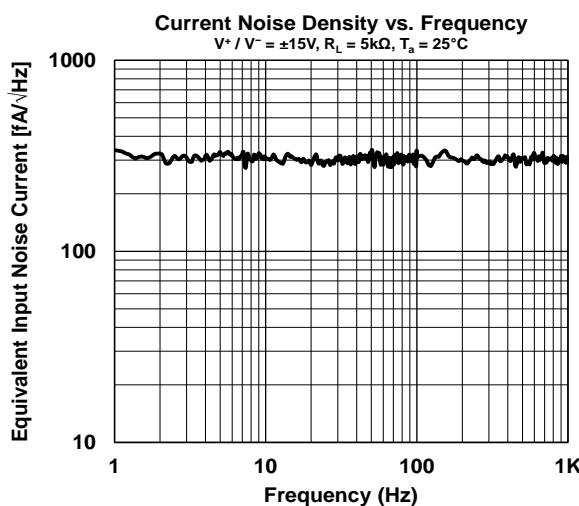
■ TYPICAL CHARACTERISTICS

Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.



■ TYPICAL CHARACTERISTICS

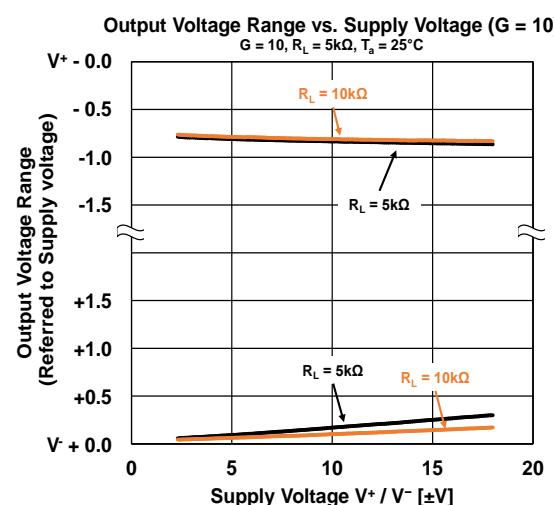
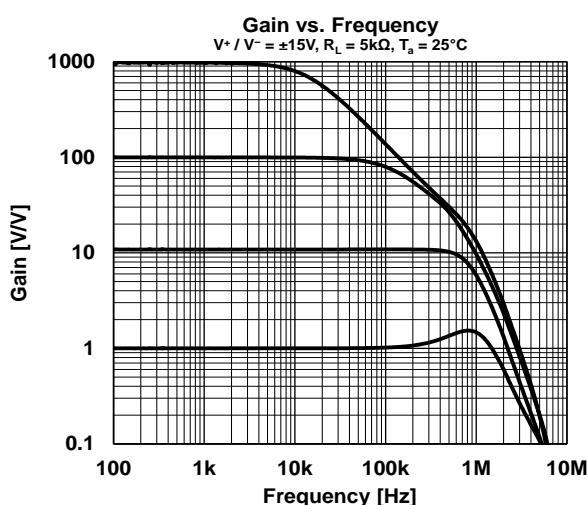
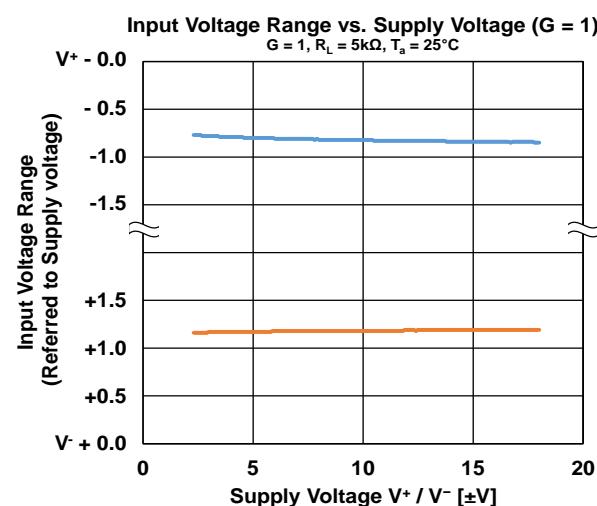
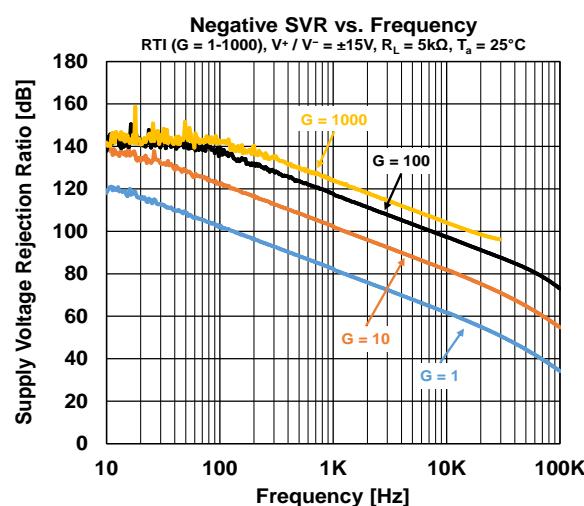
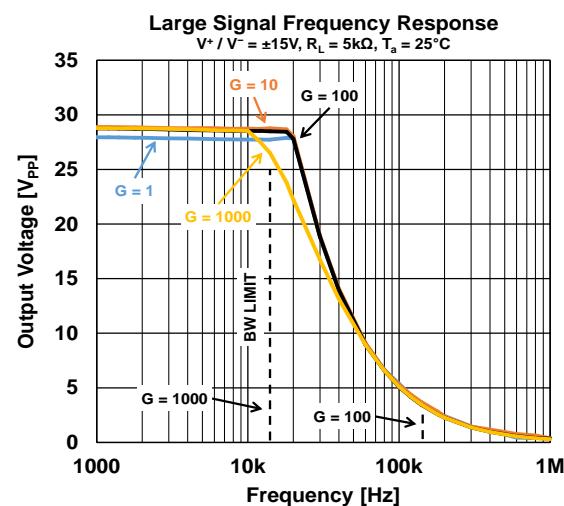
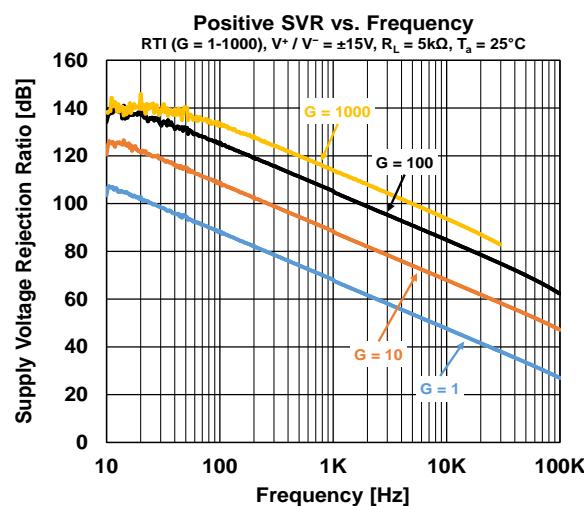
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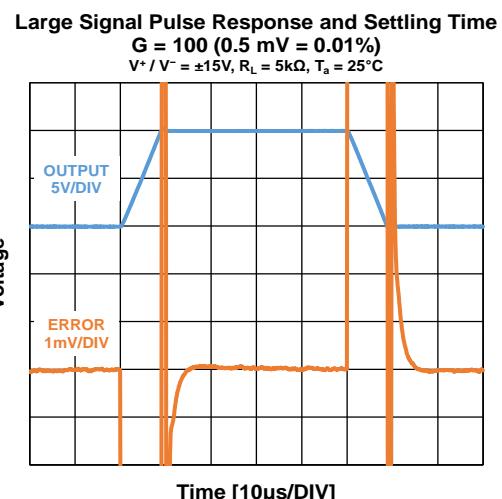
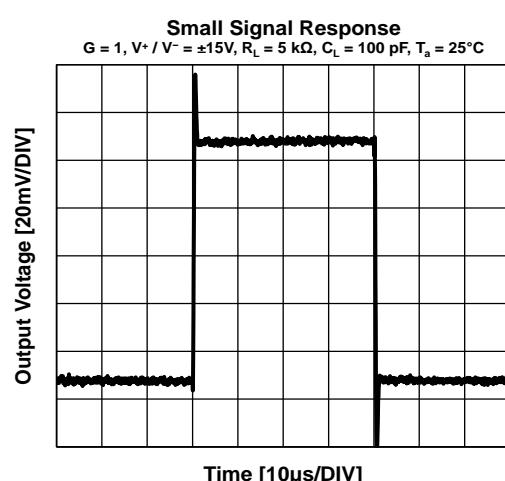
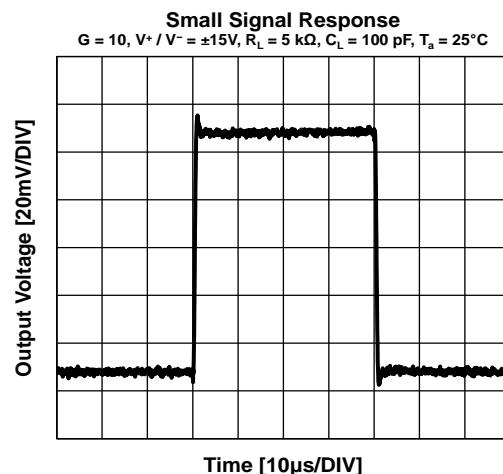
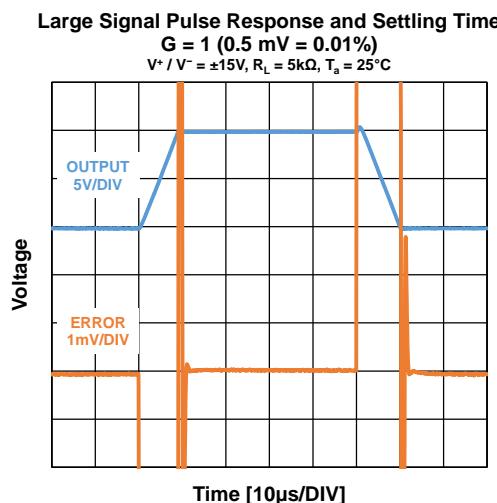
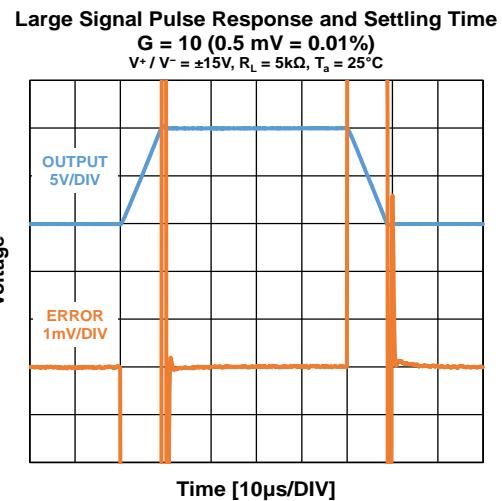
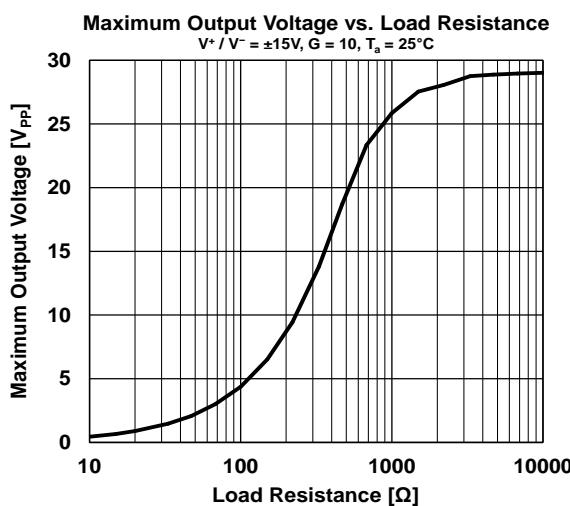
## ■ TYPICAL CHARACTERISTICS

Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.



■ TYPICAL CHARACTERISTICS

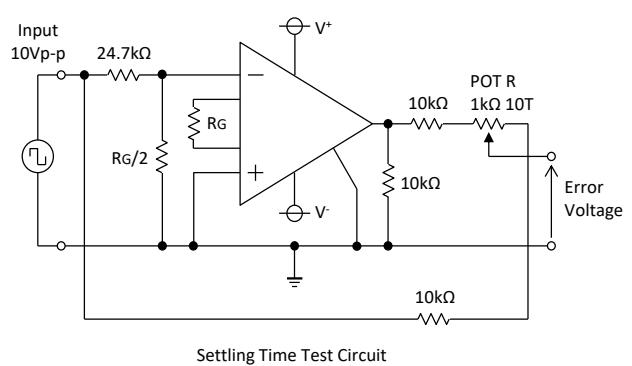
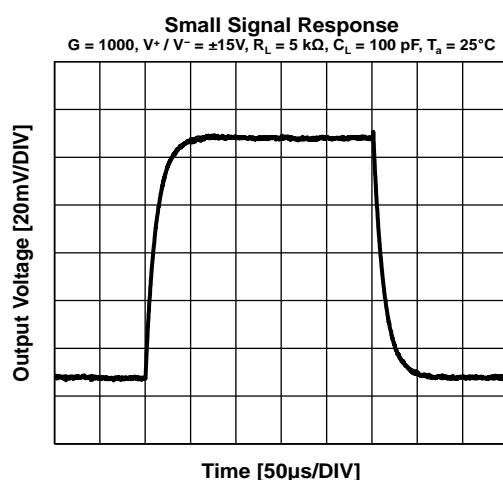
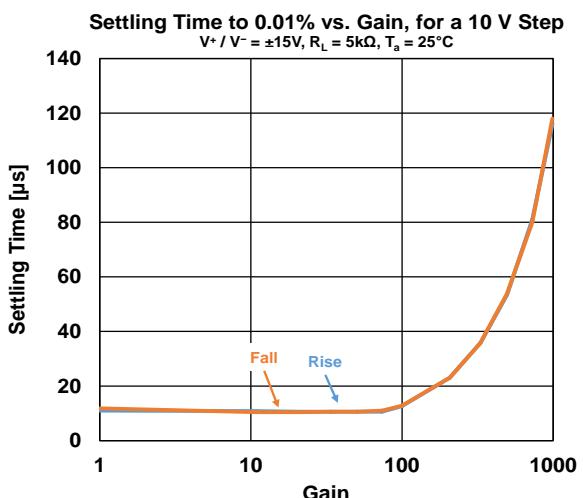
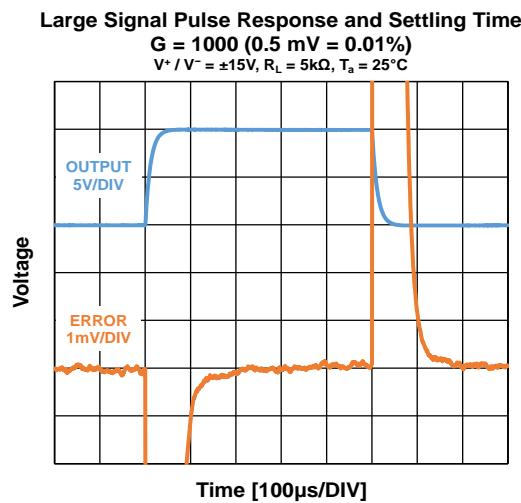
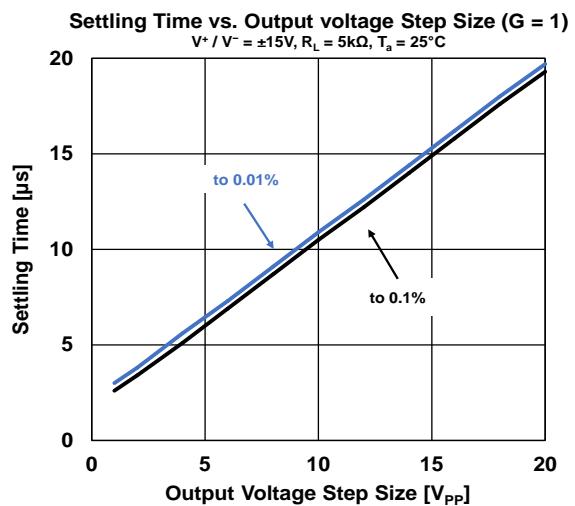
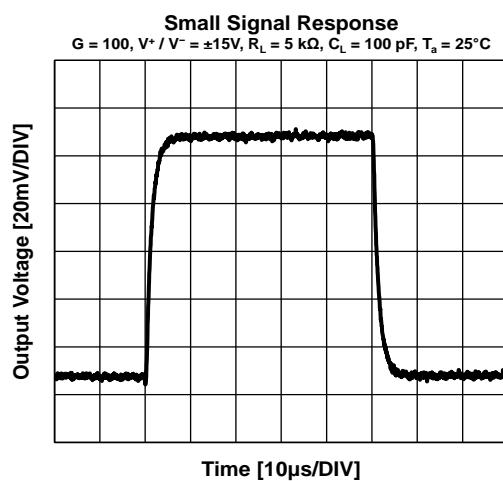
Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.



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## ■ TYPICAL CHARACTERISTICS

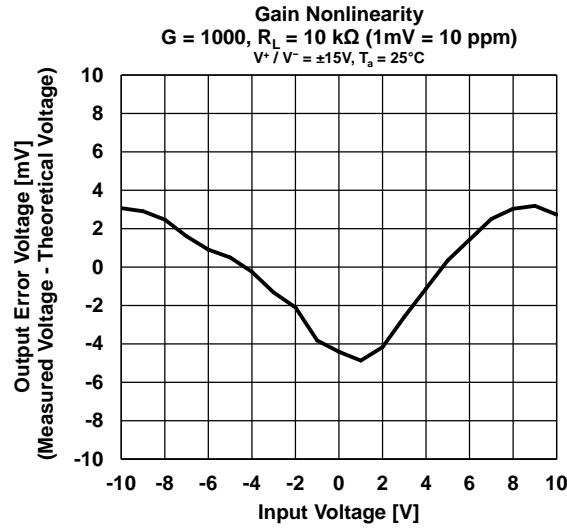
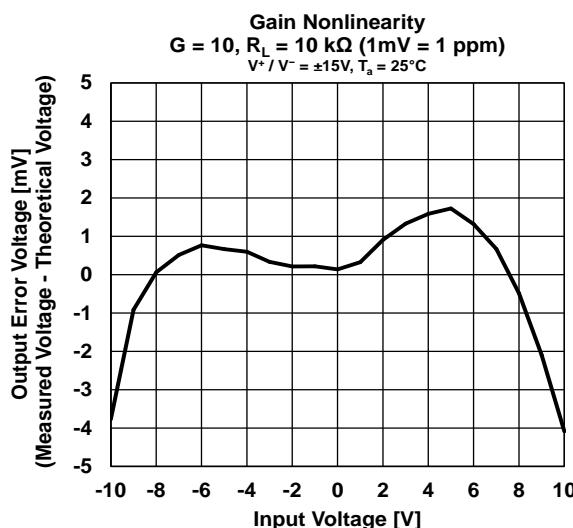
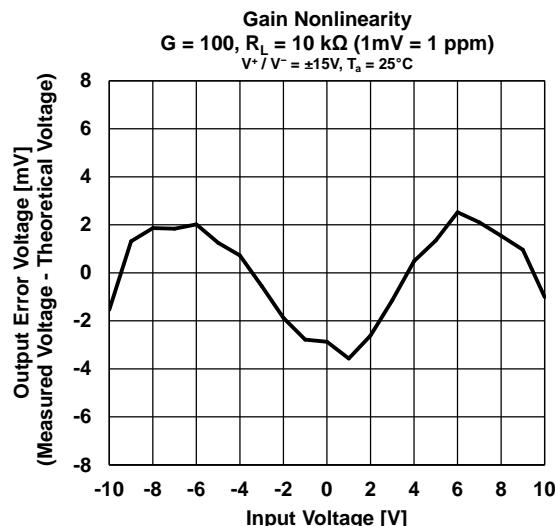
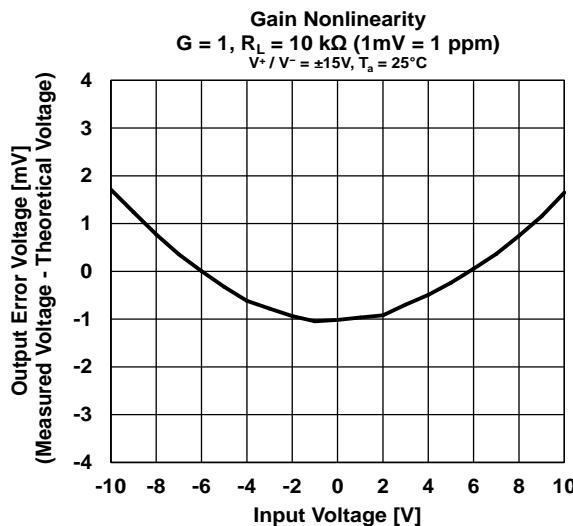
Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.



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## ■ TYPICAL CHARACTERISTICS

Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.



## ■ APPLICATION NOTES

## Theory of Operation

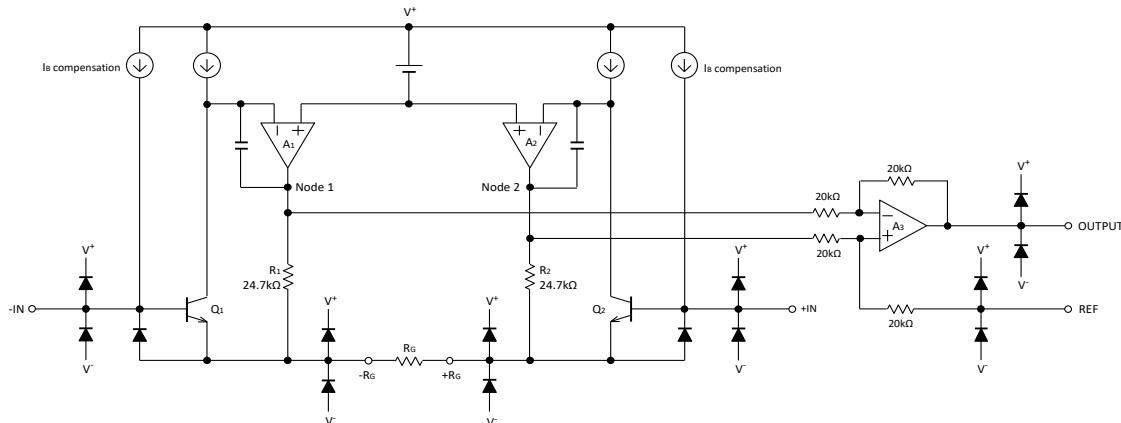


Fig.1. NL9620 Internal Block Diagram

The NL9620 is a general instrumentation amplifier consisting of three operational amplifiers. This instrumentation amplifier consists of two stages. The first stage consists of a differential amplifier circuit that amplifies differential signals, and the second stage consists of a subtraction circuit that removes common-mode signals. Fig.1 shows a Internal Block Diagram of the NL9620.

The operation of the first stage is described below. Amplifier A1 works to keep the collector of transistor Q1 at a constant voltage by the effect of a virtual short circuit. This is achieved by controlling the -RG pin to a voltage that is a diode voltage drop from the -IN pin voltage. Similarly, amplifier A2 controls the +RG pin to a voltage that is a diode voltage drop from the +IN pin voltage. As a result, a voltage equivalent to the differential input voltage is applied to both ends of the gain-setting resistor R<sub>G</sub>. The current through resistor R<sub>G</sub> is fed through resistors R<sub>1</sub> and R<sub>2</sub>, producing an amplified differential signal between the outputs of amplifiers A1 and A2.

The second stage is a  $G = 1$  subtraction circuit, consisting of amplifier A3 and four resistors. This stage removes the in-phase signal from the differential signal amplified in the first stage.

The transfer function of the NL9620 is expressed by the following equation

$$V_{OUT} = G \times (V_{IN+} - V_{IN-}) + V_{REF}$$

Here, the formula for the gain G is expressed by the following equation

$$G = 1 + \frac{49.4k\Omega}{R_G}$$

### Gain Selection

Connecting a resistor between the  $R_G$  terminals sets the gain of the NL9620. The gain can be calculated by referring to Table 1 or using the following equation relating gain to resistor  $R_G$ .

$$R_G = \frac{49.4k\Omega}{G - 1}$$

Table 1. gains set by resistors of the E96 series (tolerance  $\pm 1\%$ )

Resistor $R_G$ (1% std) [Ω]	Calculated Gain [V/V]
NC (open)	1.000
49.9k	1.990
12.4k	4.984
5.49k	10.00
2.61k	19.93
1.00k	50.40
499	100.0
249	199.4
100	495.0
49.9	991.0
24.9	1,985
9.76	5.063k
4.87	10.14k

To design for overall system gain accuracy, the resistance error and temperature drift of the resistor  $R_G$ s should be considered in conjunction with the NL9620 gain specifications. When resistor  $R_G$  is not used (open), gain error and gain drift are minimised.

### Supply Current of $R_G$

The NL9620 replicates the differential voltage between the input terminals to both ends of the resistor  $R_G$ . The size of resistor  $R_G$  must be selected to accommodate the power consumed by the resistor.

### Input and Output Offset Voltage

There are two specifications related to the offset voltage of the instrumentation amplifier: the input offset voltage  $V_{OSI}$  and the output offset voltage  $V_{Oso}$ .

In the NL9620, each offset voltage is precisely adjusted by trimming.

The influence of these two offset voltages should be considered for each gain setting. At higher gain settings, the input offset voltage  $V_{OSI}$  dominates, and at lower gain settings, the output offset voltage  $V_{Oso}$  dominates.

The instrumentation amplifier input conversion offset voltage is calculated from the following equation using  $V_{OSI}$ ,  $V_{Oso}$ , and gain  $G$ .

$$\text{Total RTI Error} = V_{OSI} + \frac{V_{Oso}}{G}$$

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## Input and Output Noise Voltage

Two types of noise voltage specifications are defined for instrumentation amplifiers: input noise voltage  $e_{ni}$  and output noise voltage  $e_{no}$ . The influence of these two types of noise voltage must be considered for each gain setting. At higher gain settings, the input noise voltage  $e_{ni}$  dominates, and at lower gain settings, the output noise voltage  $e_{no}$  dominates. The equivalent input noise voltage of the instrumentation amplifier is calculated from the following equation using  $e_{ni}$  and  $e_{no}$  and the gain  $G$ .

$$\text{Total RTI Noise} = \sqrt{(e_{ni})^2 + \left(\frac{e_{no}}{G}\right)^2}$$

## Input Voltage Range

Fig. 2 through Fig. 4, shown as example characteristics, illustrate the common-mode input voltage that should be applied to obtain the required output voltage range at each supply voltage. In the NL9620's instrumentation amplifier structure, consisting of three operational amplifiers, the differential signal is amplified in the first amplifier stage before the common-mode signal is removed in a subtraction circuit consisting of a second-stage operational amplifier and four resistors. At the internal node between the first amplifier stage and the second-stage subtraction circuit (nodes 1 and 2 in Fig. 1), the amplified differential signal is combined with the common-mode signal and the voltage drop generated by the circuit operation. In an internal circuit where this combination signal is present, the internal node may be clipped at the supply voltage and cause the circuit to malfunction, even if the instrumentation amplifier is operated under conditions that meet the input and output voltage ranges of the instrumentation amplifier.

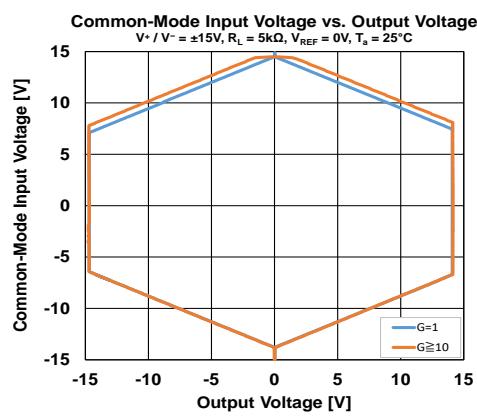


Fig.2. Input and Output Voltage range ( $V_S = \pm 15V$ )

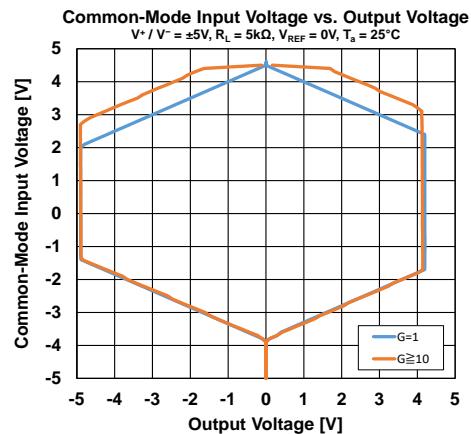


Fig.3. Input and Output Voltage range ( $V_S = \pm 5V$ )

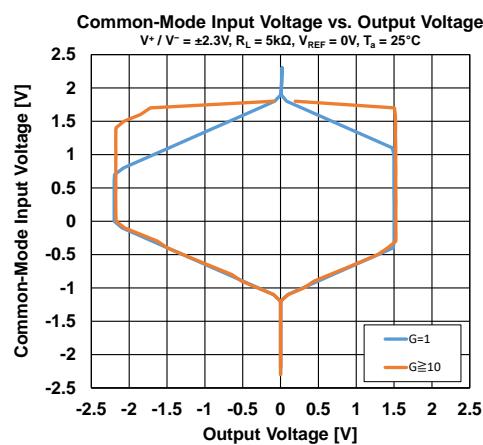


Fig.4. Input and Output Voltage range ( $V_S = \pm 2.3V$ )

### Reference Terminal

The output voltage of the NL9620 is generated with respect to the voltage applied to the REF pin. This function is useful to shift the output voltage of the instrumentation amplifier to a desired voltage level.

The impedance of the voltage source connected to the REF pin must be kept sufficiently lower than  $1\Omega$  to fully demonstrate the CMR performance of the NL9620. As shown in the simplified block diagram in fig.1,  $20\text{ k}\Omega$  is connected to the REF pin; the impedance of the voltage source connected to the REF pin adds to this  $20\text{ k}\Omega$  and affects the matching of the four resistors. This mismatch can cause gain errors and degradation of CMR and other parameters. For example, a configuration like that shown in Fig.5 can be used to provide any voltage to the REF pin of the NL9620 with a low impedance.

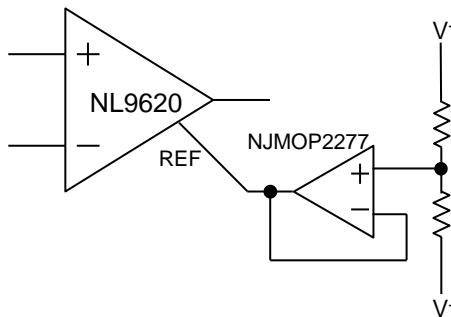


Fig.5. Example of a low impedance reference circuit.

### CMR Performance over a Wide Bandwidth

In layouts where noise problems are not taken into account, some in-phase signals may be converted to differential signals before the signals reach the input terminals of the instrumentation amplifier. The cause of in-phase to differential conversion occurs when the frequency response of one input wiring differs from that of the other input wiring.

To maintain a high CMR over a wide bandwidth, the resistors and capacitors connected to the two input leads must be closely matched.

If resistors are placed in the input wiring, such as input protection resistors, they should be placed close to the input terminals of the instrumentation amplifier. This will minimise the influence of parasitic capacitance in the PCB wiring. The parasitic capacitance of the gain setting pin also affects the frequency response of the CMR. If the PCB design includes switches, jumpers, etc. on the gain setting pins, these should be selected with the lowest possible parasitic capacitance.

**Common-Mode Rejection**

To obtain a high CMR over a wide bandwidth, the resistance and capacitance differences in the two input wires must be minimized. In environments where the influence of external noise is significant, shielded cables can be used in the transmission line. To compensate for the resistance and capacitance differences that occur at the + input and - input terminals, the lengths of the shielded cables should be matched as closely as possible.

Depending on the situation, common mode noise problems can be avoided by driving the shield portion of the cable in phase with the signal, as shown in Fig.6 and Fig.7. Driving the shield section in phase with the signal ignores the capacitance between the signal line and the shield section, and thus works to reduce the capacitance difference between the + input terminal and the - input terminal.

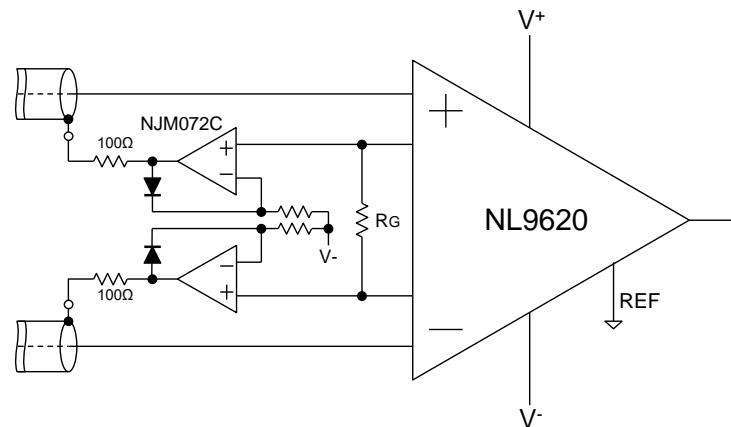


Fig.6. Differential Shield Driver

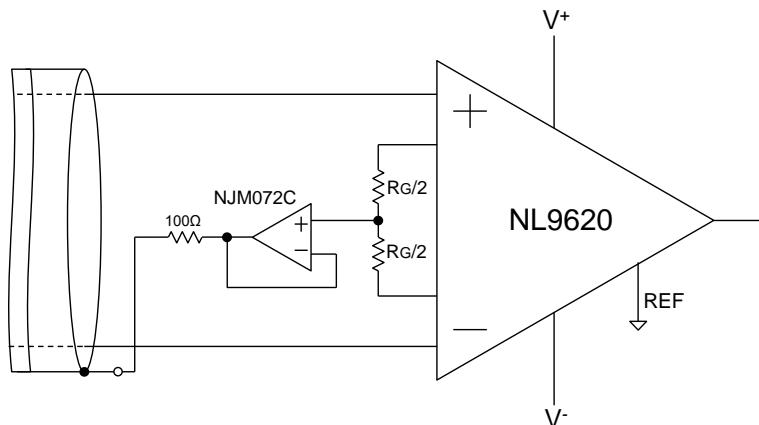


Fig.7. Common-Mode Shield Driver

**Ground Returns for Input Bias Currents**

The NL9620 generates a DC current that flows from or to the input terminals as an input bias current. (max. 2 nA) A path (return path) must be provided for the DC input bias current flowing from the input terminals to return to ground. If there is no return path, the input voltage will transition to a voltage outside the operating range, resulting in circuit malfunction.

Design the return path for the input bias current with reference to the return path example shown in Fig. 8.

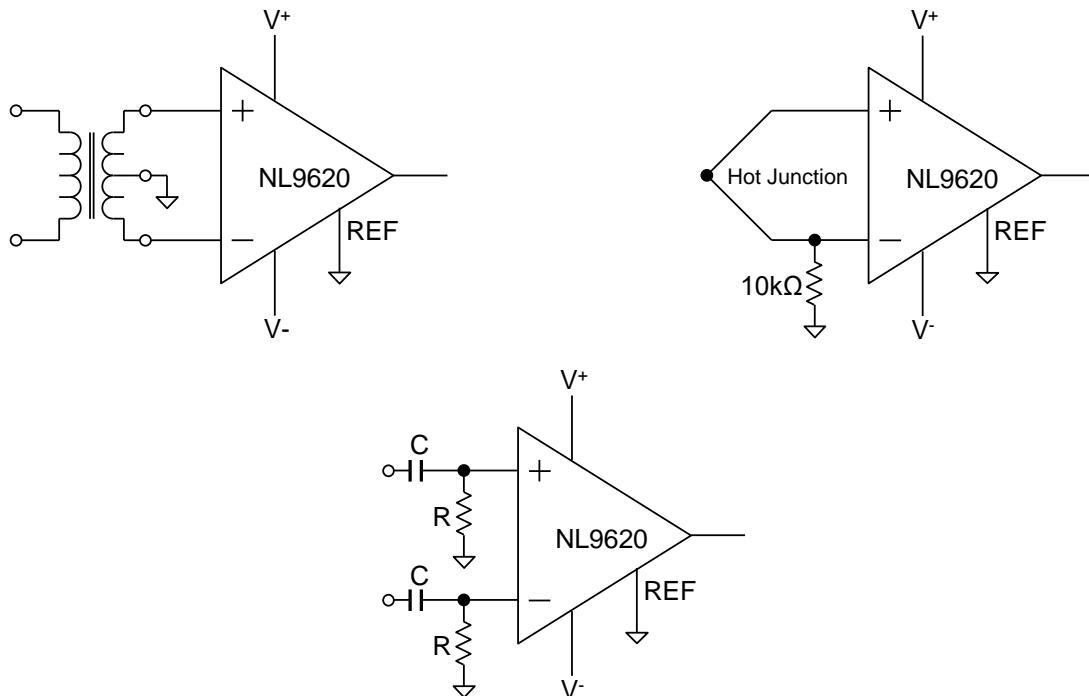


Fig.8. Examples of Ground Returns for Bias Currents

**Input Protection**

Input signals added to the NL9620 must operate within the input voltage range described in the Absolute Maximum Rated Voltage section.

**Input voltages exceeding the supply voltage**

If an input voltage in excess of the supply voltage is applied, an external resistor must be connected in series with each input terminal to limit the input current  $I_{IN}$  to within 10mA of the absolute maximum rating (Fig.9-1).

The input limiting resistor is calculated using the following formula

$$R_{PROTECT} \geq \frac{|V_{IN} - V_{SUPPLY}|}{I_{IN}}$$

Lower protection resistances may be required in applications where the effects of noise are significant: a clamp diode can be placed at the input of the NL9620 to prevent overcurrents flowing to its input terminals, resulting in a lower protection resistance value (Fig.9-2).

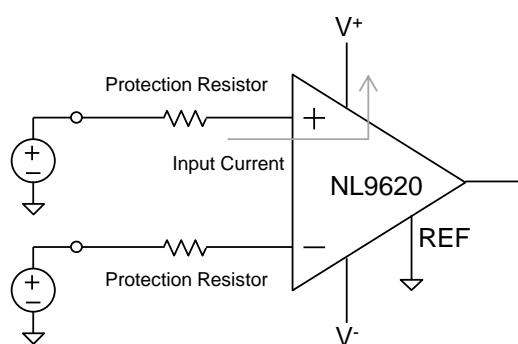


Fig.9-1. Simple Protection Circuit

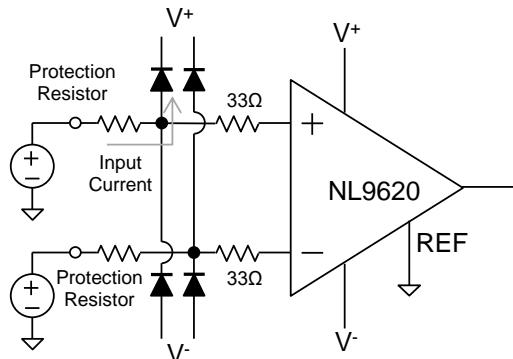


Fig.9-2. Low NOISE Protection Circuit Using Diodes

Fig.9. Example of protection circuit for Voltages Beyond Supply

### Long-term Signal Input Close to the Supply Voltage

When  $G = 1$ , a maximum differential input voltage of 36V ( $\pm 18V$ ) is allowed. Note, however, that prolonged total time with 36V applied may affect reliability. For normal use, use within the input voltage range ( $V_{ICM}$ ) shown in the electrical characteristics table.

### large Differential Input Voltage at High Gain

When large differential signals exceeding the absolute maximum ratings are input, care should be taken to avoid overvoltage at the input terminals. The input terminals of the NL9620 can be protected by using clamp diodes between the input terminals of the NL9620 as shown in Fig. 10.

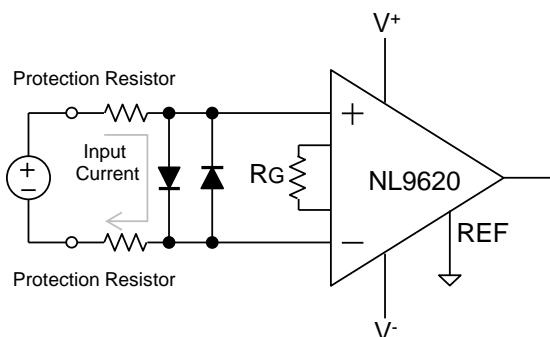


Fig.10. Protection Circuit for Large Differential Input.

**EMIRR (EMI Rejection Ratio) Definition**

The NL9620 has a built-in EMI rejection filter. As a result, it provides high-frequency noise immunity even when no external low-pass filter is connected to the input of the instrumentation amplifier. (Fig. 11 differential mode, Fig. 12 common mode)

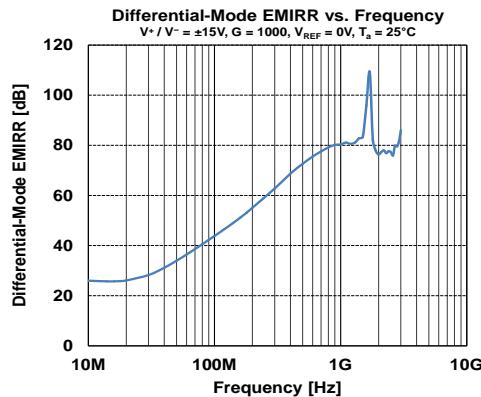


Fig.11. Differential-Mode EMIRR Characteristics

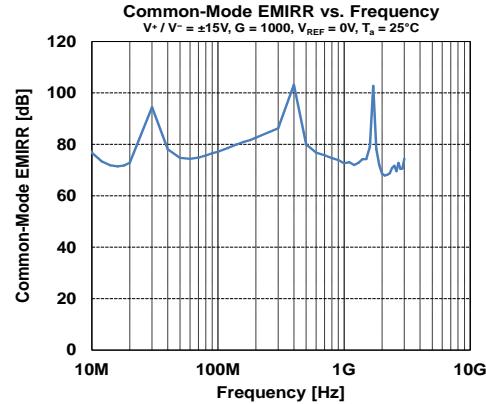


Fig.12. Common-Mode EMIRR characteristics

EMIRR is a parameter indicating the EMI robustness of an OpAmp. The definition of EMIRR is given by the following equation1.

The tolerance of the RF signal can be grasped by measuring an RF signal and offset voltage shift quantity. Offset voltage shift is small so that a value of EMIRR is big. And it understands that the tolerance for the RF signal is high. In addition, about the input offset voltage shift with the RF signal, there is the thinking that influence applied to the input terminal is dominant. Therefore, generally the EMIRR becomes value that applied an RF signal to +INPUT terminal.

$$\text{EMIRR} = 20 \cdot \log \left( \frac{V_{RF\_PEAK}}{|\Delta V_{IO}|} \right) \quad \text{--- eq.1}$$

$V_{RF\_PEAK}$ : RF Signal Amplitude [VP]

$\Delta V_{IO}$ : Input offset voltage shift quantity [V]

\*For details, refer to "Application Note for EMI Immunity" in our HP.

**Design of External RC Filter Network**

If the signal-to-noise ratio of the input signal needs to be improved by removing signals in unwanted frequency bands, it is also useful to place a filter network at the input. An example of a filter network is the RC low pass shown in Fig. 13. It is recommended that an external RC low pass filter that achieves the desired cut-off frequency  $f_c$  be designed with a  $C_D \geq 100 \text{ pF}$ . If the  $C_D$  is small, the desired cut-off frequency may not be achieved due to the influence of the EMIRR filter inside the IC.  $R$ , which generates thermal noise, should be as small as possible.

The capacitor  $C_c$  shown in Fig. 13 is used to remove common-mode noise.

For  $C_c$  to reduce common-mode noise, care should be taken to ensure that a mismatch does not occur between  $R \times C_D$  on the + input terminal and  $R \times C_c$  on the - input terminal. A mismatch converts part of the common-mode noise into differential noise and causes the signal-to-noise ratio of the signal to deteriorate.

Designing  $C_c$  using the  $C_D \geq 10C_c$  relationship as a guide can reduce the effect of mismatch.

$$\text{FilterFreq}_{\text{DIFF}} = \frac{1}{2\pi R(2C_D + C_c)}$$

$$\text{FilterFreq}_{\text{CM}} = \frac{1}{2\pi R C_c}$$

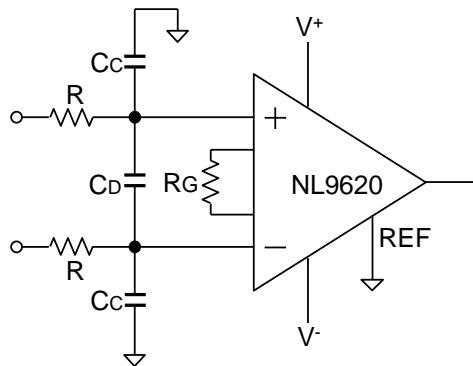


Fig.13. RC Low-Pass Filter to Improve the S/N Ratio of Input Signals

### Precision V-I Converter

Fig. 14 shows an example application for a high accuracy current source using the NL9620 instrumentation amplifier. The input bias current of the operational amplifier gives an error in the output current, so an op amp with a low input bias current should be selected.

The output current value of a V-I converter is expressed by the following equation

$$I_L = \frac{V_X}{R1} = \frac{\{(V_{IN+}) - (V_{IN-})\}G}{R1}$$

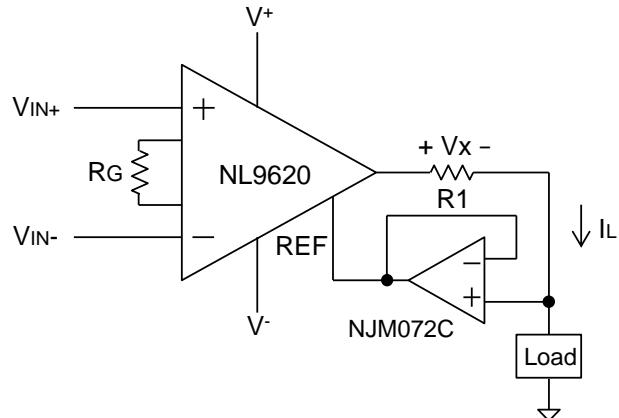
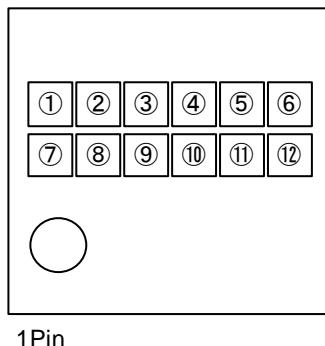


Fig.14. Precision V-I Converter Circuit Using Instrumentation Amplifier

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① to ⑦      Product Code      Refer to *Part Marking List*  
⑧ to ⑫      Lot Number      Alphanumeric Serial Number



### NOTICE

There can be variation in the marking when different AOI (Automated Optical Inspection) equipment is used. In the case of recognizing the marking characteristic with AOI, please contact our sales or distributor before attempting to use AOI.

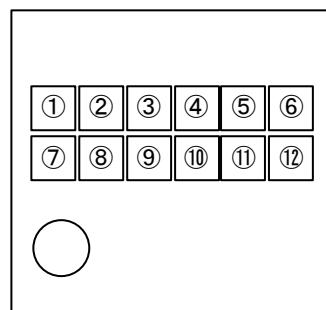
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# Nissinbo Micro Devices Inc.

## ■ MARKING SPECIFICATION (EMP-8-AN)

① to ⑦      Product Code      Refer to *Part Marking List*  
⑧ to ⑫      Lot Number      Alphanumeric Serial Number



1Pin

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### Part Marking List

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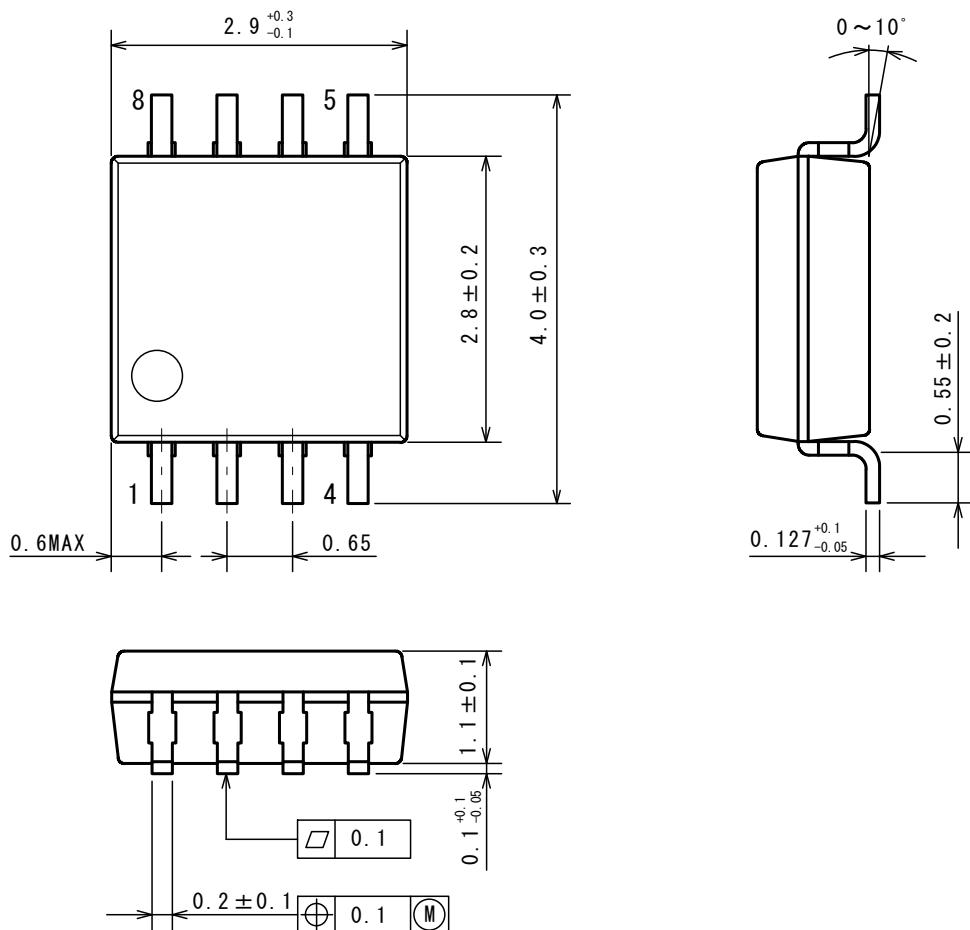
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VSP-8-AF

PI-VSP-8-AF-E-A

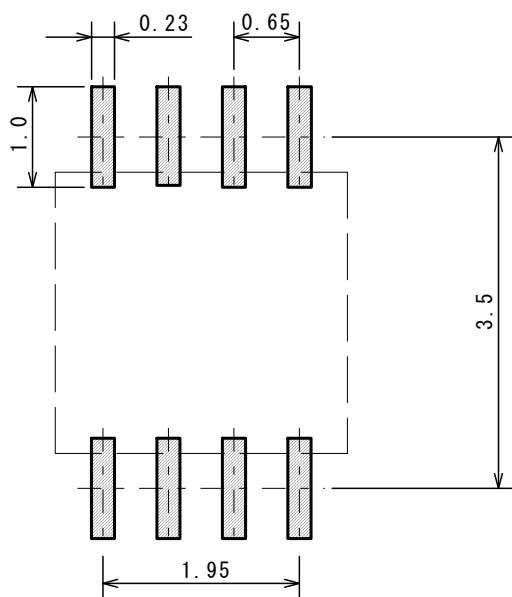
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UNIT: mm



## ■ EXAMPLE OF SOLDER PADS DIMENSIONS

UNIT: mm



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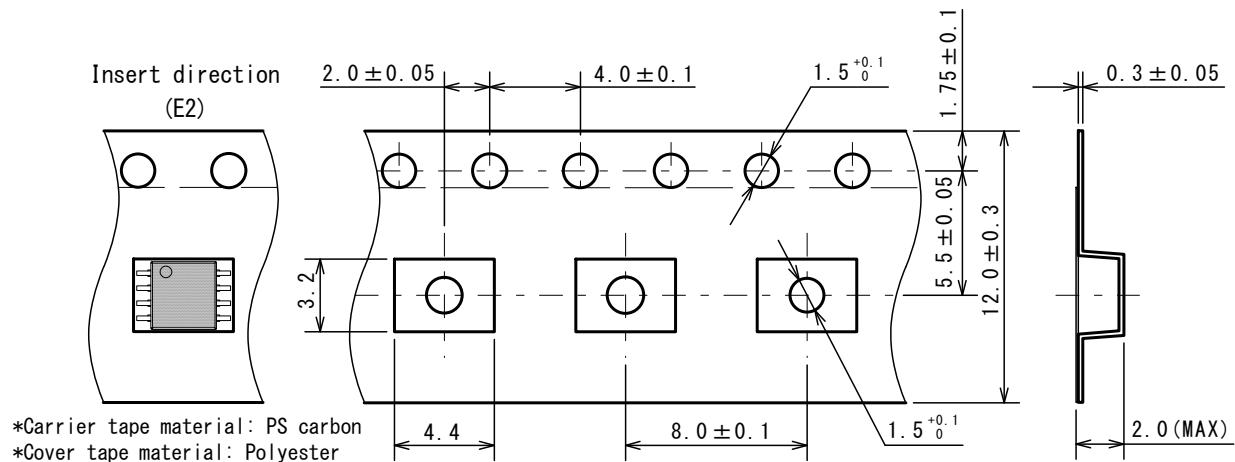
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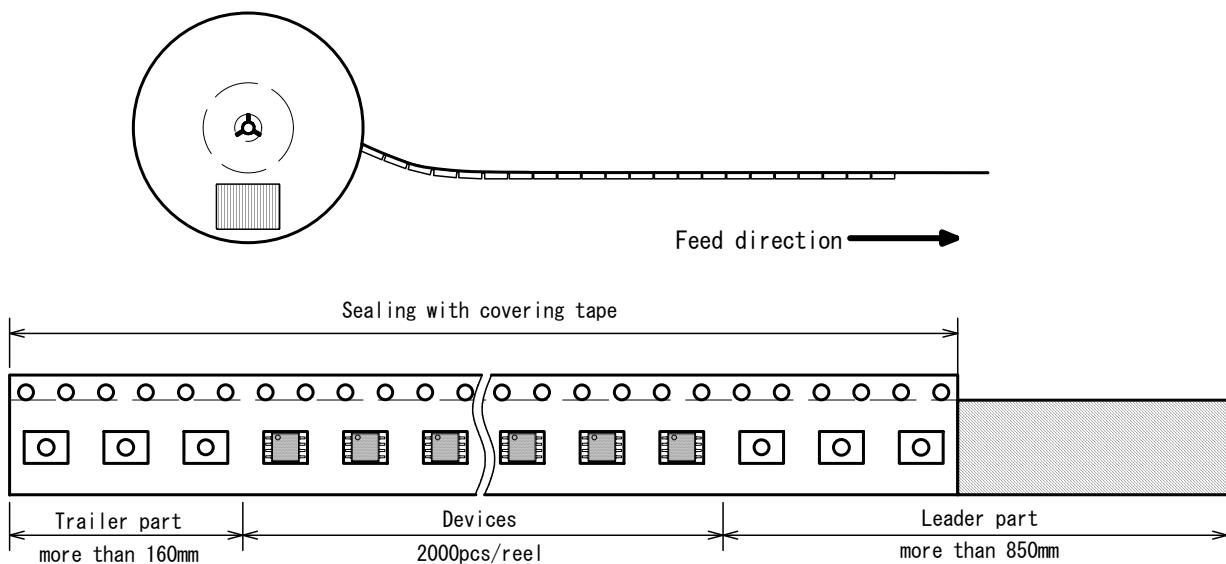
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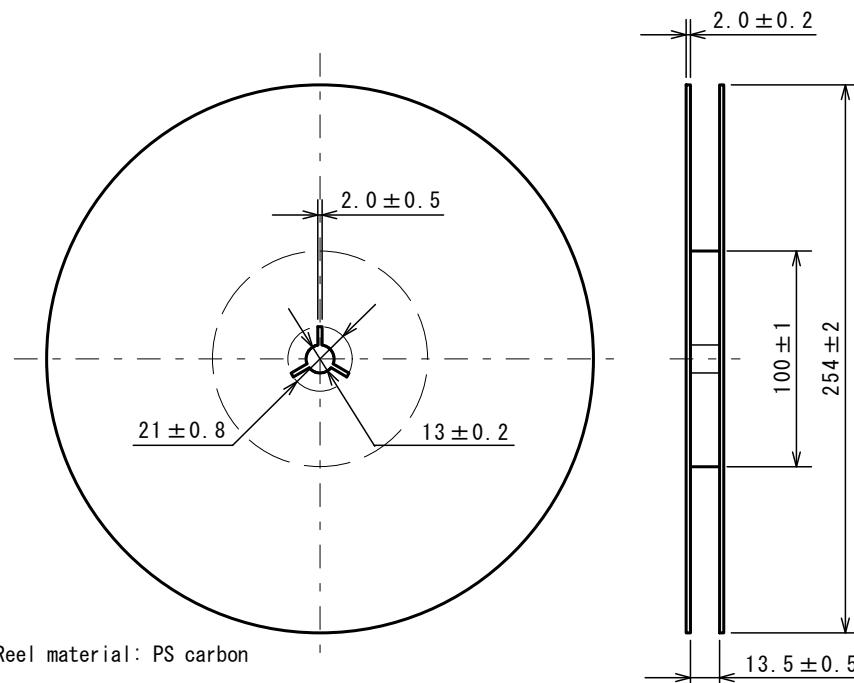


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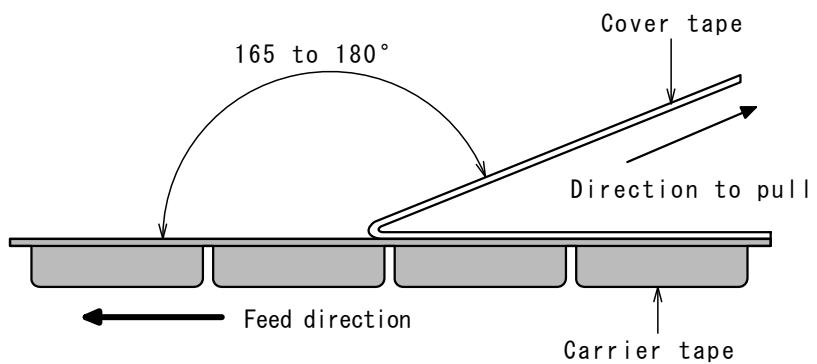


**Nissinbo Micro Devices Inc.****VSP-8-AF**

PI-VSP-8-AF-E-A

**(3) Reel dimensions****(4) Peeling strength****Peeling strength of cover tape**

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- Peeling speed 300mm/min
- Peeling strength 0.1 to 1.3N

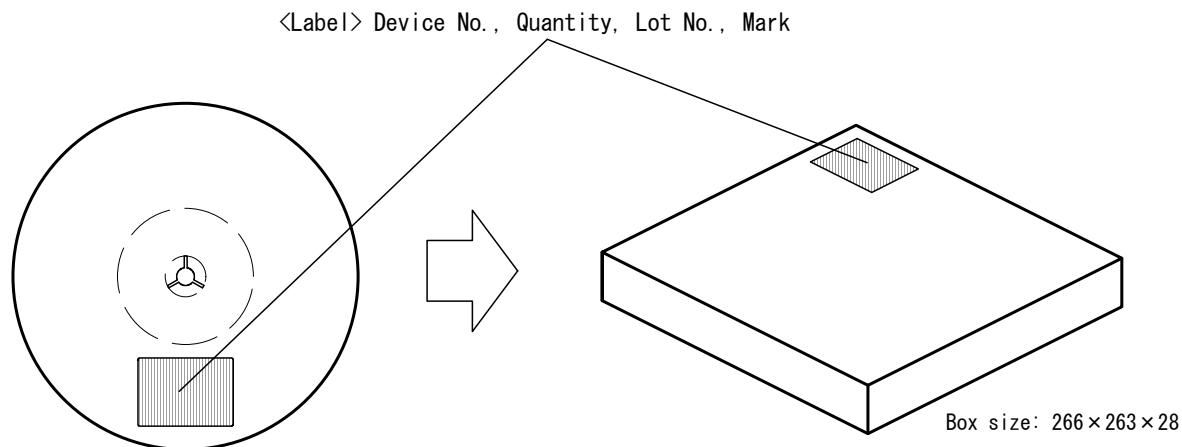
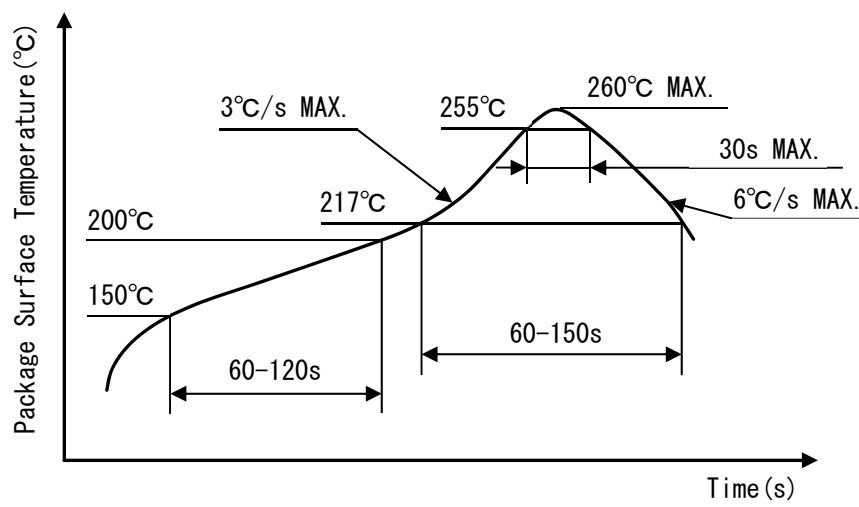


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PI-VSP-8-AF-E-A

(5) Packing state

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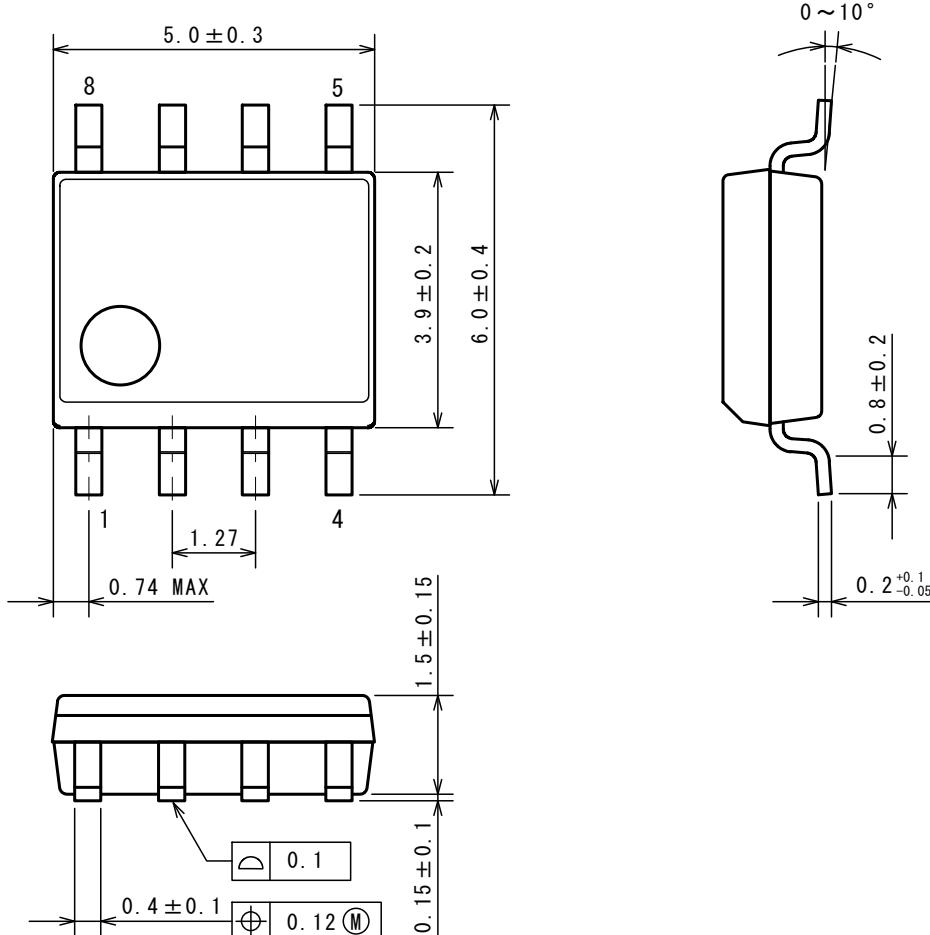
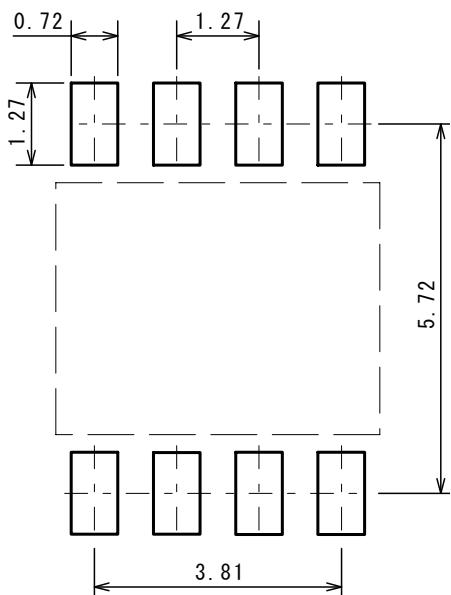
**Nissinbo Micro Devices Inc.**

EMP-8-AN

PI-EMP-8-AN-E-B

**■ PACKAGE DIMENSIONS**

UNIT: mm

**■ EXAMPLE OF SOLDER PADS DIMENSIONS**

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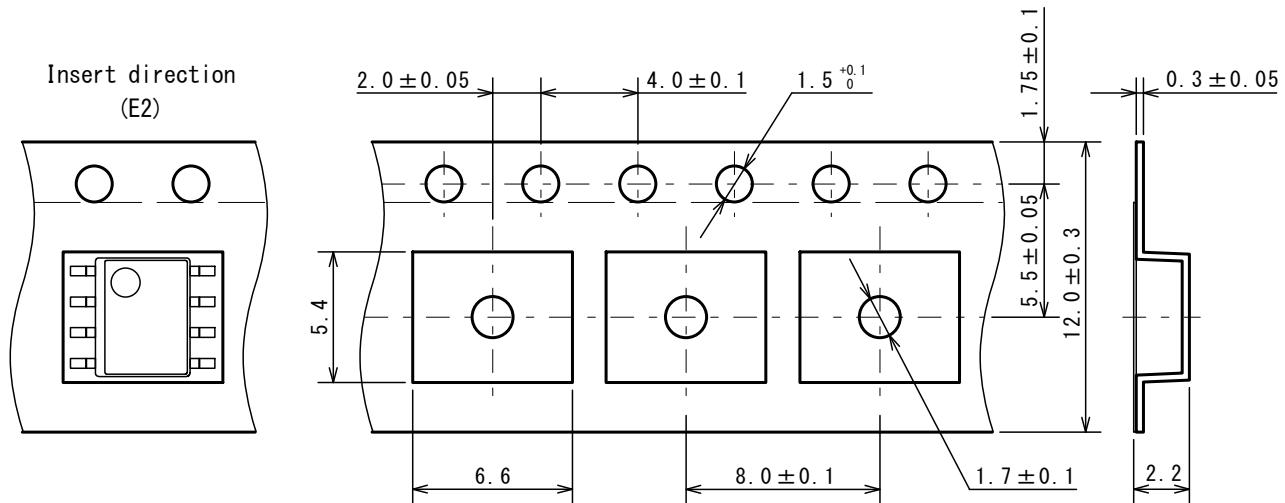
EMP-8-AN

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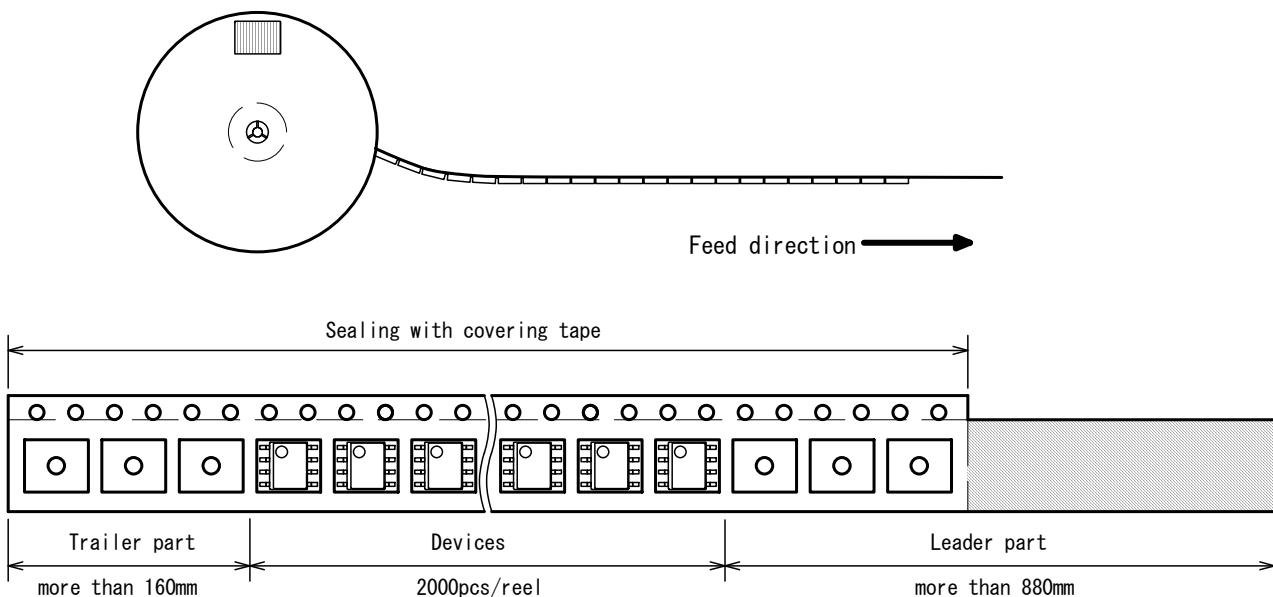
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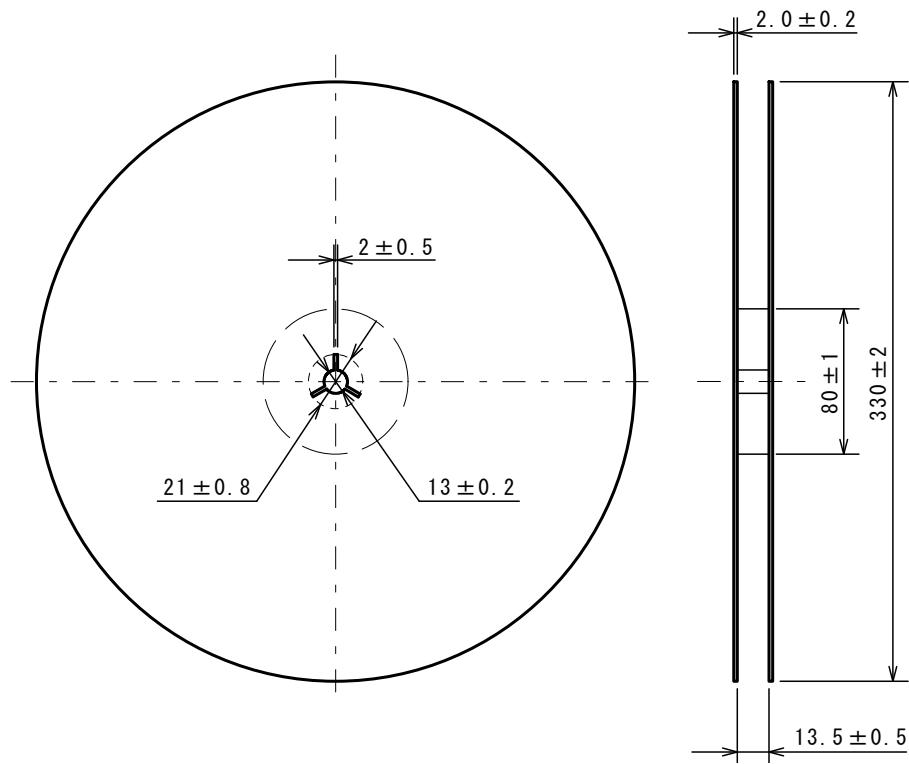


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PI-EMP-8-AN-E-B

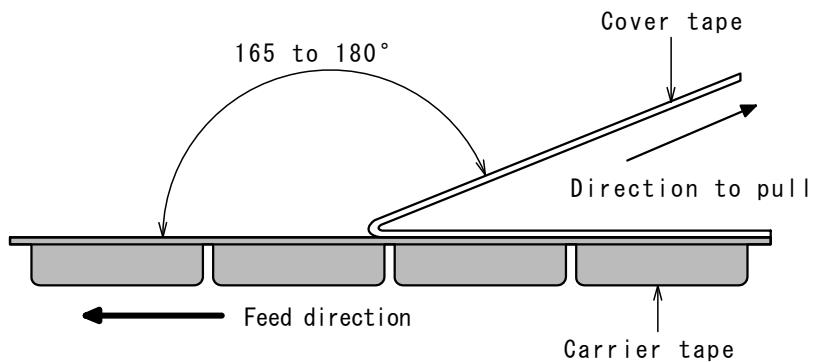
## (3) Reel dimensions



## (4) Peeling strength

## Peeling strength of cover tape

- Peeling angle 165 to 180° degrees to the taped surface.
- Peeling speed 300mm/min
- Peeling strength 0.1 to 1.3N



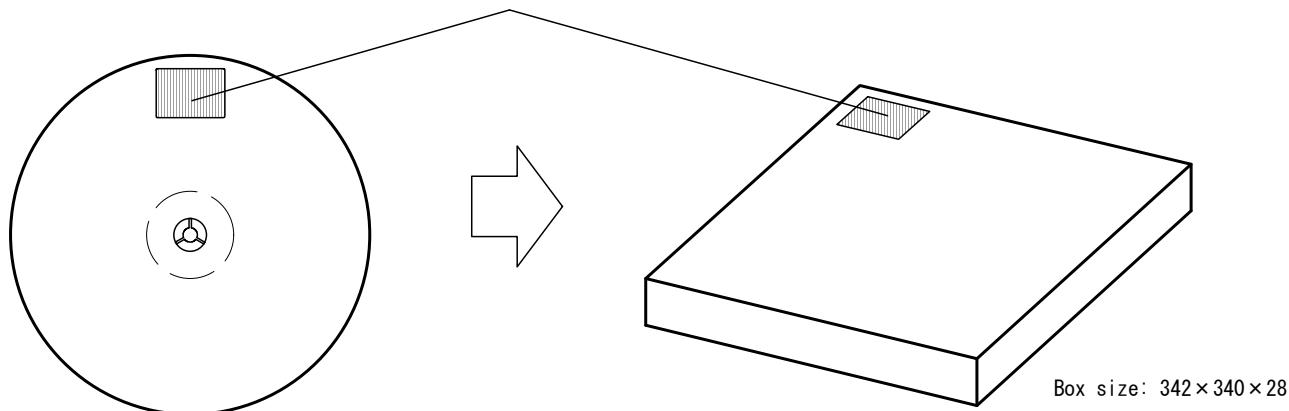
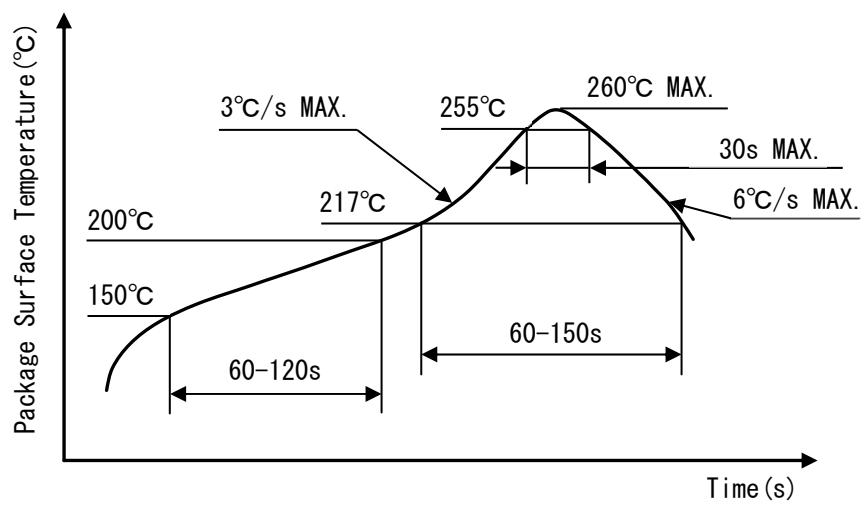
**Nissinbo Micro Devices Inc.**

EMP-8-AN

PI-EMP-8-AN-E-B

## (5) Packing state

&lt;Label&gt; Product name, Quantity, Lot No, Mark

**■ HEAT-RESISTANCE PROFILES**

# Nissinbo Micro Devices Inc.

## ■ REVISION HISTORY

Date	Revision	Contents of Changes
May 7, 2025	Ver.1.0	Initial Release

1. The products and the product specifications described in this document are subject to change or discontinuation of production without notice for reasons such as improvement. Therefore, before deciding to use the products, please refer to our sales representatives for the latest information thereon.
2. The materials in this document may not be copied or otherwise reproduced in whole or in part without the prior written consent of us.
3. This product and any technical information relating thereto are subject to complementary export controls (so-called KNOW controls) under the Foreign Exchange and Foreign Trade Law, and related politics ministerial ordinance of the law. (Note that the complementary export controls are inapplicable to any application-specific products, except rockets and pilotless aircraft, that are insusceptible to design or program changes.) Accordingly, when exporting or carrying abroad this product, follow the Foreign Exchange and Foreign Trade Control Law and its related regulations with respect to the complementary export controls.
4. The technical information described in this document shows typical characteristics and example application circuits for the products. The release of such information is not to be construed as a warranty of or a grant of license under our or any third party's intellectual property rights or any other rights.
5. The products listed in this document are intended and designed for use as general electronic components in standard applications (office equipment, telecommunication equipment, measuring instruments, consumer electronic products, amusement equipment etc.). Those customers intending to use a product in an application requiring extreme quality and reliability, for example, in a highly specific application where the failure or misoperation of the product could result in human injury or death should first contact us.
  - Aerospace Equipment
  - Equipment Used in the Deep Sea
  - Power Generator Control Equipment (nuclear, steam, hydraulic, etc.)
  - Life Maintenance Medical Equipment
  - Fire Alarms / Intruder Detectors
  - Vehicle Control Equipment (automotive, airplane, railroad, ship, etc.)
  - Various Safety Devices
  - Traffic control system
  - Combustion equipment

In case your company desires to use this product for any applications other than general electronic equipment mentioned above, make sure to contact our company in advance. Note that the important requirements mentioned in this section are not applicable to cases where operation requirements such as application conditions are confirmed by our company in writing after consultation with your company.

6. We are making our continuous effort to improve the quality and reliability of our products, but semiconductor products are likely to fail with certain probability. In order to prevent any injury to persons or damages to property resulting from such failure, customers should be careful enough to incorporate safety measures in their design, such as redundancy feature, fire containment feature and fail-safe feature. We do not assume any liability or responsibility for any loss or damage arising from misuse or inappropriate use of the products.
7. The products have been designed and tested to function within controlled environmental conditions. Do not use products under conditions that deviate from methods or applications specified in this datasheet. Failure to employ the products in the proper applications can lead to deterioration, destruction or failure of the products. We shall not be responsible for any bodily injury, fires or accident, property damage or any consequential damages resulting from misuse or misapplication of the products.
8. Quality Warranty

#### 8-1. Quality Warranty Period

In the case of a product purchased through an authorized distributor or directly from us, the warranty period for this product shall be one (1) year after delivery to your company. For defective products that occurred during this period, we will take the quality warranty measures described in section 8-2. However, if there is an agreement on the warranty period in the basic transaction agreement, quality assurance agreement, delivery specifications, etc., it shall be followed.

#### 8-2. Quality Warranty Remedies

When it has been proved defective due to manufacturing factors as a result of defect analysis by us, we will either deliver a substitute for the defective product or refund the purchase price of the defective product.

Note that such delivery or refund is sole and exclusive remedies to your company for the defective product.

#### 8-3. Remedies after Quality Warranty Period

With respect to any defect of this product found after the quality warranty period, the defect will be analyzed by us. On the basis of the defect analysis results, the scope and amounts of damage shall be determined by mutual agreement of both parties. Then we will deal with upper limit in Section 8-2. This provision is not intended to limit any legal rights of your company.

9. Anti-radiation design is not implemented in the products described in this document.
10. The X-ray exposure can influence functions and characteristics of the products. Confirm the product functions and characteristics in the evaluation stage.
11. WLCSP products should be used in light shielded environments. The light exposure can influence functions and characteristics of the products under operation or storage.
12. Warning for handling Gallium and Arsenic (GaAs) products (Applying to GaAs MMIC, Photo Reflector). These products use Gallium (Ga) and Arsenic (As) which are specified as poisonous chemicals by law. For the prevention of a hazard, do not burn, destroy, or process chemically to make them as gas or power. When the product is disposed of, please follow the related regulation and do not mix this with general industrial waste or household waste.
13. Please contact our sales representatives should you have any questions or comments concerning the products or the technical information.



Nisshinbo Micro Devices Inc.

Official website

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